Journal of Crystal Growth 117 (1992) 1084–1099
North-Holland

JOURNAL OF CRYSTAL GROWTH

Author index

Abramof, E., see Kudlek 117 (1992) 290
Adachi, S., see Takeyama 117 (1992) 1081
Adams, S.J.A., see Simpson 117 (1992) 134
Adams, S.J.A., see Wallace 117 (1992) 320
Aguekian, V.F., see Takeyama 117 (1992) 1081
Akimoto, K., see Okuyama 117 (1992) 139
Akimoto, K., H. Okuyama, M. Ikeda and Y. Mori, Oxygen doping in CdTe, CdS and ZnS 117 (1992) 420
Akimoto, K., see Miyajima 117 (1992) 694
Akimoto, K., see Nakano 117 (1992) 797
Akiyama, H., see Tokizaki 117 (1992) 603
Al Allak, H.M., see Simmons 117 (1992) 959
Allen, J.W, see Zheng 117 (1992) 358
Alnajjar, A.A., see Loginov 117 (1992) 259
Alnajjar, A.A., C.C.R. Watson, A.W. Brinkman and K. Durose, Post-growth doping of bulk CdTe crystals with phosphorus 117 (1992) 385
Ando, K., see Ohki 117 (1992) 102
Ando, K., J. Palmer, A. Ohki, S. Tohno and S. Zembutsu, Interface defect characteristics of Zn(SSe)–ZnSe and ZnSe–(ZnCd)S hetero-epitaxial systems 117 (1992) 560
Ando, M. and Y.A. Ono, Temperature effects in the emission characteristics of CaS:Eu thin-film electroluminescent devices 117 (1992) 969
Ando, S., T. Okada, S. Endo, T. Irie, T. Miya and H. Nakanishi, Edge emission enhancement in CdS by laminated $CdInGaS_4$ 117 (1992) 362
André, R., see Cibert 117 (1992) 424
Anno, H., T. Koyanagi and K. Matsubara, Epitaxial growth of zincblende MnTe films as a new magneto-optical material 117 (1992) 816
Arai, H., see Nakahara 117 (1992) 830
Archer, N.A., H.D. Palfrey and A.F.W. Willoughby, The influence of dislocations on mercury self-diffusion in epitaxial and bulk grown $Cd_xHg_{1-x}Te$ 117 (1992) 177
Armitage, D.N., H.M. Yates, J.O. Williams, D.J. Cole-Hamilton and I.P. Patterson, ZnS grown by metalorganic chemical vapour deposition (MOCVD) on GaAs-(100) using t-butyl mercaptan and dimethylzinc 117 (1992) 1082
Arterton, B., see Viney 117 (1992) 806
Arterton, B., J.W. Brightwell, S. Mason, B. Ray and I.V.F. Viney, Impact of phase concentrations on structure and electroluminescence of ZnS:Cu 117 (1992) 1008
As, D.J., see Hingerl 117 (1992) 341
Ashenford, D.E., P. Devine, J.H.C. Hogg, B. Lunn, C.G. Scott and M. Verma, Variations in the structural and electrical properties as a function of depth in CdTe layers grown on InSb substrates 117 (1992) 233
Ashenford, D.E., see Jackson 117 (1992) 867
Aslam, N., E.D. Jones, T.C.Q. Noakes, J.B. Mullin and A.F.W. Willoughby, The diffusion of zinc in cadmium telluride 117 (1992) 249
Astles, M.A., see Berlouis 117 (1992) 918
Astles, M.G., N. Shaw, G. Blackmore and R.S. Hall, Improved control of composition and electrical properties of liquid phase epitaxial (CdHg)Te layers 117 (1992) 213
Aulombard, R.L., see Pagés 117 (1992) 569
Austin, R.F., see Doran 117 (1992) 465
Azoulay, M., S. Rotter, G. Gafni, R. Tenne and M. Roth, Zinc segregation in CdZnTe grown under Cd/Zn partial pressure control 117 (1992) 276

Bagot, D., S. Rolland, R. Granger and R. Triboulet, Linear thermal expansion coefficient in $Hg_{1-x}Cd_xTe$ and $Hg_{1-x}Zn_xTe$ 117 (1992) 189
Ballutaud, D., see Marbeuf 117 (1992) 197
Baltramiejūnas, S. Pakalnis and G. Tamulaitis, Transient effects in photoexcited CdS microcrystals 117 (1992) 622
Banyai, L., see Uhrig 117 (1992) 598
Baranyuk, V.Ye., see Kosyachenko 117 (1992) 583
Barthou, C., see Zeinert 117 (1992) 1016
Bassani, F., K. Saminadayar, S. Tatarenko, K. Kheng, R.T. Cox, N. Magnea and C. Grattepain, Indium doping of CdTe layers and $CdTe/Cd_{1-x}Zn_xTe$ microstructures 117 (1992) 391
Bauer, G., see Enichlmair 117 (1992) 844
Bauer, S., A. Rosenauer, J. Skorsetz, W. Kuhn, H.P. Wagner, J. Zweck and W.

Journal of Crystal Growth 117 (1992) 1084–1099
North-Holland

JOURNAL OF CRYSTAL GROWTH

Author index

Abramof, E., see Kudlek 117 (1992) 290
Adachi, S., see Takeyama 117 (1992) 1081
Adams, S.J.A., see Simpson 117 (1992) 134
Adams, S.J.A., see Wallace 117 (1992) 320
Aguekian, V.F., see Takeyama 117 (1992) 1081
Akimoto, K., see Okuyama 117 (1992) 139
Akimoto, K., H. Okuyama, M. Ikeda and Y. Mori, Oxygen doping in CdTe, CdS and ZnS 117 (1992) 420
Akimoto, K., see Miyajima 117 (1992) 694
Akimoto, K., see Nakano 117 (1992) 797
Akiyama, H., see Tokizaki 117 (1992) 603
Al Allak, H.M., see Simmons 117 (1992) 959
Allen, J.W, see Zheng 117 (1992) 358
Alnajjar, A.A., see Loginov 117 (1992) 259
Alnajjar, A.A., C.C.R. Watson, A.W. Brinkman and K. Durose, Post-growth doping of bulk CdTe crystals with phosphorus 117 (1992) 385
Ando, K., see Ohki 117 (1992) 102
Ando, K., J. Palmer, A. Ohki, S. Tohno and S. Zembutsu, Interface defect characteristics of Zn(SSe)–ZnSe and ZnSe–(ZnCd)S hetero-epitaxial systems 117 (1992) 560
Ando, M. and Y.A. Ono, Temperature effects in the emission characteristics of CaS:Eu thin-film electroluminescent devices 117 (1992) 969
Ando, S., T. Okada, S. Endo, T. Irie, T. Miya and H. Nakanishi, Edge emission enhancement in CdS by laminated $CdInGaS_4$ 117 (1992) 362
André, R., see Cibert 117 (1992) 424
Anno, H., T. Koyanagi and K. Matsubara, Epitaxial growth of zincblende MnTe films as a new magneto-optical material 117 (1992) 816
Arai, H., see Nakahara 117 (1992) 830
Archer, N.A., H.D. Palfrey and A.F.W. Willoughby, The influence of dislocations on mercury self-diffusion in epitaxial and bulk grown $Cd_xHg_{1-x}Te$ 117 (1992) 177
Armitage, D.N., H.M. Yates, J.O. Williams, D.J. Cole-Hamilton and I.P. Patterson, ZnS grown by metalorganic chemical vapour deposition (MOCVD) on GaAs-(100) using t-butyl mercaptan and dimethylzinc 117 (1992) 1082
Arterton, B., see Viney 117 (1992) 806
Arterton, B., J.W. Brightwell, S. Mason, B. Ray and I.V.F. Viney, Impact of phase concentrations on structure and electroluminescence of ZnS:Cu 117 (1992) 1008
As, D.J., see Hingerl 117 (1992) 341
Ashenford, D.E., P. Devine, J.H.C. Hogg, B. Lunn, C.G. Scott and M. Verma, Variations in the structural and electrical properties as a function of depth in CdTe layers grown on InSb substrates 117 (1992) 233
Ashenford, D.E., see Jackson 117 (1992) 867
Aslam, N., E.D. Jones, T.C.Q. Noakes, J.B. Mullin and A.F.W. Willoughby, The diffusion of zinc in cadmium telluride 117 (1992) 249
Astles, M.A., see Berlouis 117 (1992) 918
Astles, M.G., N. Shaw, G. Blackmore and R.S. Hall, Improved control of composition and electrical properties of liquid phase epitaxial (CdHg)Te layers 117 (1992) 213
Aulombard, R.L., see Pagés 117 (1992) 569
Austin, R.F., see Doran 117 (1992) 465
Azoulay, M., S. Rotter, G. Gafni, R. Tenne and M. Roth, Zinc segregation in CdZnTe grown under Cd/Zn partial pressure control 117 (1992) 276

Bagot, D., S. Rolland, R. Granger and R. Triboulet, Linear thermal expansion coefficient in $Hg_{1-x}Cd_xTe$ and $Hg_{1-x}Zn_xTe$ 117 (1992) 189
Ballutaud, D., see Marbeuf 117 (1992) 197
Baltramiejūnas, S. Pakalnis and G. Tamulaitis, Transient effects in photoexcited CdS microcrystals 117 (1992) 622
Banyai, L., see Uhrig 117 (1992) 598
Baranyuk, V.Ye., see Kosyachenko 117 (1992) 583
Barthou, C., see Zeinert 117 (1992) 1016
Bassani, F., K. Saminadayar, S. Tatarenko, K. Kheng, R.T. Cox, N. Magnea and C. Grattepain, Indium doping of CdTe layers and $CdTe/Cd_{1-x}Zn_xTe$ microstructures 117 (1992) 391
Bauer, G., see Enichlmair 117 (1992) 844
Bauer, S., A. Rosenauer, J. Skorsetz, W. Kuhn, H.P. Wagner, J. Zweck and W.

Gebhardt, Investigation of strained ZnTe epilayers by high resolution electron microscopy 117 (1992) 297
Bell, W., A.E.D. McQueen, J.C. Walton, D.F. Foster, D.J. Cole-Hamilton and J.E. Hails, Decomposition and reactivity of tellurium alkyls in the liquid and gas phases; dihex-5-enyltellurium and dipent-4-enyltellurium as mechanistic probes 117 (1992) 58
Benalloul, P., see Zeinert 117 (1992) 1016
Benhlal, J.T., R. Granger, D. Lemoine, R. Triboulet and Y. Marqueton, Irreversible optical response in $Cd_{1-x}Zn_xTe$ mixed crystals 117 (1992) 281
Benoit, J., see Zeinert 117 (1992) 1016
Benz, K.W., see Meyer 117 (1992) 656
Berlouis, L.E.A., L.M. Peter, R. Greef and M.A. Astles, In-situ spectroscopic characterisation of passivation layers on (Cd,Hg)Te 117 (1992) 918
Bhargava, R.N., Compact blue lasers in the near future 117 (1992) 894
Bhat, I.B., Recent advances in the organometallic vapor phase epitaxial growth of HgCdTe by the direct alloy growth process 117 (1992) 1
Bicknell-Tassius, R.N., see Kuhn 117 (1992) 660
Bicknell-Tassius, R.N., see Waag 117 (1992) 820
Bicknell-Tassius, R.N., see Yakovlev 117 (1992) 854
Bicknell-Tassius, R.N., see Kuhn 117 (1992) 871
Bicknell-Tassius, R.N., see Uraltsev 117 (1992) 877
Bilger, G., see Mauch 117 (1992) 964
Binder, R., see Masumoto 117 (1992) 732
Blackmore, G., see Astles 117 (1992) 213
Bleuse, J., see Pautrat 117 (1992) 454
Bleuse, J., N. Magnea, L. Ulmer, J.L. Pautrat and H. Mariette, Room-temperature laser emission near 2 μm from an optically pumped HgCdTe separate-confinement heterostructure 117 (1992) 1046
Bonnafé, J., see Triboulet 117 (1992) 227
Bonnet, J.E., see Marbeuf 117 (1992) 197
Bouchenaki, C., see Ullrich 117 (1992) 902
Bouchenaki, C., see Ullrich 117 (1992) 925
Bowers, K.A., see Ren 117 (1992) 510
Boyce, P.J., see Nakano 117 (1992) 331
Brandt, G.B., see Kun 117 (1992) 987
Bratina., G., see Vanzetti 117 (1992) 573
Brightwell, J.W., see Viney 117 (1992) 806
Brightwell, J.W., see Arterton 117 (1992) 1008
Brinkman, A.W., see Loginov 117 (1992) 259
Brinkman, A.W., see Alnajjar 117 (1992) 385
Brinkman, A.W., see Simmons 117 (1992) 959
Briot, O., see Pagés 117 (1992) 569
Britt, J., see Chu 117 (1992) 1073
Broser, I., see Hoffmann 117 (1992) 640
Broser, I., see Podlowski 117 (1992) 698
Broser, I., see Thurian 117 (1992) 727
Broser, I., see Fricke 117 (1992) 783
Broser, I., Ch. Fricke, B. Lummer, R. Heitz, H. Perls and A. Hoffmann, Optical nonlinearity and fast switching due to birefringence and mode coupling in CdS crystals 117 (1992) 788
Brown, P.D., see Loginov 117 (1992) 259
Brown, P.D., Y.Y. Loginov, K. Durose, J.T. Mullins, T. Taguchi, T. Burbery, S. Lawson-Jack and I. Jones, Microstructural properties of epitaxial CdS, (Cd,Zn)S and CdS ‖(Cd,Zn)S superlattices 117 (1992) 536
Brown, P.D., see Loginov 117 (1992) 682
Burbery, T., see Brown 117 (1992) 536
Bureyev, A.V., see Butkhuzi 117 (1992) 366
Buskes, H., see Hartley 117 (1992) 166
Busse, W., see Hommel 117 (1992) 721
Butkhuzi, T.V., A.V. Bureyev, A.N. Georgobiani, N.P. Kekelidze and T.G. Khulordava, Optical and electrical properties of radical beam gettering epitaxy grown n- and p-type ZnO single crystals 117 (1992) 366
Butkhuzi, T.V., A.N. Georgobiani, B.T. Eltazarov, T.G. Khulordava and M.B. Kotljarevsky, Blue light emitting diodes on the base of ZnSe single crystals 117 (1992) 1055

Cammack, D., see Olego 117 (1992) 324
Carr, D., see Hartley 117 (1992) 166
Cavenett, B.C., see Simpson 117 (1992) 134
Cavenett, B.C., see Wallace 117 (1992) 320
Cesnulevicius, J., see Woggon 117 (1992) 608
Chamarro, M.A., C. Gourdon and P. Lavallard, Photoluminescence polarization properties of CdS_xSe_{1-x} nanocrystals in glasses: evidence for hexagonal structure 117 (1992) 614
Chang, S.K., see Lee 117 (1992) 148
Chang, S.K., C.D. Lee, H.L. Park and C.H. Chung, Exciton transfer processes in $ZnSe_{1-x}Te_x$ 117 (1992) 793
Chen, X., see O'Donnell 117 (1992) 497
Chen, X., see Trager-Cowan 117 (1992) 532
Cheng, H., see DePuydt 117 (1992) 1078
Chu, S.S., see Chu 117 (1992) 1073
Chu, T.L., S.S. Chu, C. Ferekides, C.Q. Wu, J. Britt and C. Wang, High efficiency thin film CdS/CdTe heterojunction solar cells 117 (1992) 1073
Chung, C., F. Jain and G. Drake, Prospects of fabricating blue/green lasers using ZnSe based metal–insulator–semiconductor (MIS) heterostructures 117 (1992) 1062
Chung, C.H., see Lee 117 (1992) 148
Chung, C.H., see Chang 117 (1992) 793
Cibert, J., R. André, C. Deshayes, Le Si Dang, H. Okumura, S. Tatarenko, G. Feuillet, P.H. Jouneau, R. Mallard and

K. Saminadayar, Piezoelectric fields in CdTe-based heterostructures 117 (1992) 424
Cloitre, T., see Pagés 117 (1992) 569
Cockayne, B., see Dhese 117 (1992) 91
Cockayne, B., see Parbrook 117 (1992) 492
Cockayne, B., see O'Donnell 117 (1992) 497
Cockayne, B., see Trager-Cowan 117 (1992) 532
Cole-Hamilton, D.J., see Bell 117 (1992) 58
Cole-Hamilton, D.J., see Armitage 117 (1992) 1082
Cook, Jr., J.W., see Ren 117 (1992) 510
Cox, R.T., see Bassani 117 (1992) 391
Cui, Jie, Hailong Wang and Fuxi Gan, The optical and spectroscopic properties of II–VI wide-gap ZnSe/ZnS and ZnSe/ZnTe strained-layer superlattices 117 (1992) 505

Dang, Le Si, see Cibert 117 (1992) 424
Daniel, G., see Schmidt 117 (1992) 748
Das, S.K., see Morris 117 (1992) 929
Davies, J.J., see Dhese 117 (1992) 91
Davies, J.J., see Nakano 117 (1992) 331
De Orúe, M.A., see Vogel 117 (1992) 710
Deleporte, C., see Dubowski 117 (1992) 862
DePuydt, J.M., M.A. Haase, J. Qiu and H. Cheng, ZnSe-based laser diodes 117 (1992) 1078
Deshayes, C., see Cibert 117 (1992) 424
Devine, P., see Ashenford 117 (1992) 233
Dhese, K., J.E. Nicholls, J. Goodwin, W.E. Hagston, J.J. Davies, M.P. Halsall, B. Cockayne and P.J. Wright, Atmospheric pressure metalorganic chemical vapour deposition growth and optical studies of $ZnSe_{1-x}Te_x$ thin film alloys 117 (1992) 91
Dietl, T., see Enichlmair 117 (1992) 844
Ding, J., see Ren 117 (1992) 510
Ding, J., see Xie 117 (1992) 1079
Donegan, J.F., see Doran 117 (1992) 465
Doran, J.P., J.F. Donegan, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Thermal broadening of excitons in CdZnTe/ZnTe single quantum wells 117 (1992) 465
Drake, G., see Chung 117 (1992) 1062
Dreyhsig, J., see Zeinert 117 (1992) 1016
Druilhe, R., see Marbeuf 117 (1992) 10
Dubowski, J.J., A.P. Roth, E. Deleporte, G. Peter, Z.C. Feng and S. Perkowitz, Optical properties of CdTe–$Cd_{0.90}Mn_{0.10}Te$ multiple quantum well structures grown by pulsed laser evaporation and epitaxy 117 (1992) 862
Durand, A., see Triboulet 117 (1992) 227
Durose, K., see Loginov 117 (1992) 259
Durose, K., see Alnajjar 117 (1992) 385
Durose, K., see Brown 117 (1992) 536
Durose, K., see Loginov 117 (1992) 682
Durose, K., see Simmons 117 (1992) 959
Dvoretsky, S.A., see Sabinina 117 (1992) 238

Ebe, H., see Tanaka 117 (1992) 24
Ekawa, M., K. Yasuda, M. Okada, T. Ferid, A. Tanaka and M. Saji, Mechanism of arsenic incorporation in MOVPE growth of CdTe layers 117 (1992) 254
Eltazarov, B.T., see Butkhuzi 117 (1992) 1055
Endo, S., see Ando 117 (1992) 362
Endo, Y., see Takada 117 (1992) 44
Enichlmair, H., K. Kaltenegger, H. Krenn, G. Bauer, T. Dietl and J. Humenberger, Light-induced magnetization in $Hg_{1-x}Cd_xTe$ 117 (1992) 844
Era, K., see Minami 117 (1992) 565
Era, K., see Inoue 117 (1992) 738
Erland, J., see Pantke 117 (1992) 763
Ezaki, T., see Nishimura 117 (1992) 119

Fan, G.H., see Guan 117 (1992) 515
Fan, G.H., see Shen 117 (1992) 519
Fan, G.H., see Zhang 117 (1992) 523
Fan, X.W., see Guan 117 (1992) 515
Fan, X.W., see Shen 117 (1992) 519
Fan, X.W., see Zhang 117 (1992) 523
Feldman, R.D., see Doran 117 (1992) 465
Feng, Z.C., see Dubowski 117 (1992) 862
Ferekides, C., see Chu 117 (1992) 1073
Ferid, T., see Ekawa 117 (1992) 254
Feuillet, G., see Cibert 117 (1992) 424
Fillard, J.P., see Triboulet 117 (1992) 227
Filz, Th., see Kolodziejczyk 117 (1992) 549
Flores, M.L., see Vogel 117 (1992) 710
Fluegel, B., see Koch 117 (1992) 592
Fluegel, B., see Masumoto 117 (1992) 732
Fluegel, B., see Sasaki 117 (1992) 768
Folkard, M.A., see Hartley 117 (1992) 166
Foster, D.F., see Bell 117 (1992) 58
Franciosi, A., see Vanzetti 117 (1992) 573
Fricke, Ch., see Hoffmann 117 (1992) 640
Fricke, Ch., U. Neukirch, R. Heitz, A. Hoffmann and I. Broser, Recombination kinetics of CdS:In 117 (1992) 783
Fricke, Ch., see Broser 117 (1992) 788
Fujii, S., see Terada 117 (1992) 54
Fujii, T., see Yoshida 117 (1992) 75
Fujii, Y., see Suemune 117 (1992) 1068
Fujii, Y., see O'Donnell 117 (1992) 1077
Fujimoto, M., see Suemune 117 (1992) 1068
Fujisaki, Y., see Ohishi 117 (1992) 125
Fujita, Sg., see Fujita 117 (1992) 67
Fujita, Sg., see Ichino 117 (1992) 527
Fujita, Sg., see Funato 117 (1992) 543
Fujita, Sg., see Ichimura 117 (1992) 689
Fujita, Sz. and Sg. Fujita, Photo-assisted metalorganic vapor phase epitaxial growth of wide-gap II–VI semiconductors 117 (1992) 67
Fujita, Sz., see Ichino 117 (1992) 527

Fujita, Sz., see Funato 117 (1992) 543
Fujita, Sz., see Ichimura 117 (1992) 689
Fujita, Y., see Terada 117 (1992) 54
Fujiwara, H., see Gotoh 117 (1992) 85
Fujiyasu, H., see Tatsuoka 117 (1992) 554
Fujiyasu, H., see Suzuki 117 (1992) 881
Fujiyasu, H., Y. Takeuchi, K. Hikida, K. Ishino and A. Ishida, Mn doped ZnS and ZnS–CdS superlattice double insulating electroluminescent devices made by hot wall epitaxy 117 (1992) 1026
Funato, M., M. Ishii, P.A. Murawala, O. Tsuji, Sz. Fujita and Sg. Fujita, Metalorganic vapor phase epitaxial growth and characterization of ZnSe–GaAs multilayered structures 117 (1992) 543
Furukawa, Y., see Oguri 117 (1992) 116
Furukawa, Y., see Isshiki 117 (1992) 410
Furumiya, M., see Itoh 117 (1992) 835

Gafni, G., see Azoulay 117 (1992) 276
Gall, P., see Triboulet 117 (1992) 227
Galun, E., G. Hodes, M. Peisach, E. Muranevich and R. Tenne, Shallow donor state removal via photoelectrochemical etching in Cd(Se,Te) 117 (1992) 666
Gan, Fuxi, see Cui 117 (1992) 505
Gao, Q.Z., J. Mita, T. Tsuruoka, M. Kobayashi and K. Kawamura, High luminance white EL devices using SrS:Ce,Eu,K films deposited in a H_2 atmosphere 117 (1992) 983
Gaponenko, S., see Uhrig 117 (1992) 598
Gebhardt, W., see Bauer 117 (1992) 297
Gebhardt, W., see Wagner 117 (1992) 303
Georgobiani, A.N., see Butkhuzi 117 (1992) 366
Georgobiani, A.N., see Butkhuzi 117 (1992) 1055
Germanenko, A.V., G.M. Min'kov and O.E. Rut, Acceptor states in the dilute magnetic semiconductor p-HgMnTe with $E_g > 0$ under uniaxial stress 117 (1992) 850
Giriat, W., see Homyonfer 117 (1992) 1080
Göbel, E.O., see Yakovlev 117 (1992) 854
Godlewski, M. and K. Świątek, Excitonic processes in II–VI compounds doped with transition metal and rare earth impurities 117 (1992) 634
Goede, O., see Heimbrodt 117 (1992) 859
Goede, O., W. Heimbrodt, Th. Köpp, H.-E. Gumlich and B. Lunn, Magneto-optical anisotropy of CdTe/(Cd,Mn)Te quantum-well structures due to lattice-misfit induced strain 117 (1992) 886
Goodwin, J., see Dhese 117 (1992) 91
Goodwin, J., see Jackson 117 (1992) 867
Gotoh, J., H. Fujiwara, H. Shirai, J. Hanna and I. Shimizu, Low-temperature growth of ZnSe-based pseudomorphic structures by hydrogen-radical-enhanced chemical vapor deposition 117 (1992) 85
Gourdon, C., see Chamarro 117 (1992) 614
Granger, R., see Bagot 117 (1992) 189
Granger, R. and C.M. Pelletier, Electron mobility evaluation in $Hg_{1-x}Cd_xTe$ and $Hg_{1-x}Zn_xTe$ with two-optical-mode dispersion 117 (1992) 203
Granger, R., see Rolland 117 (1992) 208
Granger, R., see Benhlal 117 (1992) 281
Grattepain, C., see Bassani 117 (1992) 391
Greef, R., see Berlouis 117 (1992) 918
Gregory, T.J., see Heimbrodt 117 (1992) 859
Gregory, T.J., see Jackson 117 (1992) 867
Gresslehner, K.H., see Lang 117 (1992) 954
Grillo, D.C., see Xie 117 (1992) 1079
Gruzintsev, A.N., V.T. Volkov and A.N. Pronin, Investigation of luminescence centers of unactivated CaS films 117 (1992) 975
Guan, Z.P., J.H. Zhang, G.H. Fan and X.W. Fan, Excitonic transition of (ZnSe–ZnS)/CaF_2 strained-layer superlattices under lower excitation 117 (1992) 515
Guimarães, F.E.G., see Heuken 117 (1992) 336
Guimarães, F.E.G., J. Söllner, K. Marquardt, M. Heuken and K. Heime, Optical investigations and optimization of ZnSe/ZnS multi-quantum wells grown by MOVPE 117 (1992) 1075
Gumlich, H.-E., see Waldmann 117 (1992) 715
Gumlich, H.-E., see Hommel 117 (1992) 721
Gumlich, H.-E., Heimbrodt 117 (1992) 859
Gumlich, H.-E., see Goede 117 (1992) 886
Gumlich, H.-E., see Zeinert 117 (1992) 1016
Gunshor, R.L., see Nurmikko 117 (1992) 432
Gunshor, R.L., see Xie 117 (1992) 1079
Gutakovsky, A.K., see Sabinina 117 (1992) 238
Gutowski, J., see Kudlek 117 (1992) 290
Gutowski, J., see Kudlek 117 (1992) 309
Gutowski, J., see Schmolke 117 (1992) 650

Haase, M.A., see DePuydt 117 (1992) 1078
Hagston, W.E., see Dhese 117 (1992) 91
Hagston, W.E., see Jackson 117 (1992) 867
Hails, J.E., see Bell 117 (1992) 58
Halden, E., see Müller 117 (1992) 948
Hall, R.S., see Astles 117 (1992) 213
Halsall, M.P., see Dhese 117 (1992) 91
Hamakawa, Y., see Hyun 117 (1992) 587
Hamakawa, Y., see Sohn 117 (1992) 907
Hamakawa, Y., see Noma 117 (1992) 1030
Hanna, J., see Gotoh 117 (1992) 85
Harada, H., see Konishi 117 (1992) 939
Hartley, R.H., M.A. Folkard, D. Carr, P.J. Orders, D. Rees, I.K. Varga, V. Kumar, G. Shen, T.A. Steele, H. Buskes and J.B.

Lee, Ellipsometry: a technique for real time monitoring and analysis of MBE-grown CdHgTe and CdTe/HgTe superlattices 117 (1992) 166
Hatano, K., see Kumazaki 117 (1992) 285
Haugstad, G., see Vanzetti 117 (1992) 573
Hayashi, T., see Misawa 117 (1992) 617
Hegarty, J., see Doran 117 (1992) 465
Heimbrodt, W., O. Goede, Th. Köpp, K. Hieke, H.-E. Gumlich, Th. Pier, B. Lunn and T. Gregory, Magneto-optical study of asymmetric CdTe/(Cd,Mn)Te double-quantum-well nanostructures 117 (1992) 859
Heimbrodt, W., see Goede 117 (1992) 886
Heime, K., see Heuken 117 (1992) 336
Heime, K., see Guimarães 117 (1992) 1075
Heitz, R., see Hoffmann 117 (1992) 640
Heitz, R., see Thurian 117 (1992) 727
Heitz, R., see Fricke 117 (1992) 783
Heitz, R., see Broser 117 (1992) 788
Heller, C., see Ullrich 117 (1992) 902
Henderson, B., see Parbrook 117 (1992) 492
Henderson, B., see O'Donnell 117 (1992) 497
Henderson, B., see Trager-Cowan 117 (1992) 532
Herrmann, K.H., K.-P. Möllmann and J.W. Tomm, Broadening mechanisms near the E_0 transition in narrow-gap $Hg_{1-x}Cd_xTe$ ($0.2 < x < 0.6$) 117 (1992) 758
Heuken, M., J. Söllner, F.E.G. Guimarães, K. Marquardt and K. Heime, Reduced incorporation of unintentional impurities and intrinsic defects in ZnSe and ZnS grown by MOVPE 117 (1992) 336
Heuken, M., see Guimarães 117 (1992) 1075
Hieke, K., see Heimbrodt 117 (1992) 859
Hikida, K., see Fujiyasu 117 (1992) 1026
Hingerl, K., see Kudlek 117 (1992) 290
Hingerl, K., see Kudlek 117 (1992) 309
Hingerl, K., W. Jantsch, P. Juza, M. Lang, H. Sitter, J. Lilja, M. Pessa, D.J. As and W. Rothemund, Determination of acceptor binding energies in ZnSe 117 (1992) 341
Hingerl, K., see Imai 117 (1992) 406
Hirahara, K., see Shigenaka 117 (1992) 37
Hirahara, K., see Shigenaka 117 (1992) 49
Hiramatsu, M., see Matsushima 117 (1992) 328
Hishida, Y., T. Toda and T. Yamaguchi, Characteristics of Li- and Cl-doped ZnTe grown by molecular beam epitaxy 117 (1992) 396
Hobbs, A., see Sugiyama 117 (1992) 161
Hobbs, A., see Ueda 117 (1992) 266
Hobbs, A., O. Ueda, I. Sugiyama and H. Takigawa, Dislocation interactions in CdTe/GaAs grown by hot wall epitaxy with CdTe/CdZnTe superlattices 117 (1992) 475
Hodes, G., see Galun 117 (1992) 666
Hoffmann, A., B. Lummer, Ch. Fricke, R. Heitz and I. Broser, Fast relaxation phenomena in Ni-doped II–VI compounds 117 (1992) 640
Hoffmann, A., see Podlowski 117 (1992) 698
Hoffmann, A., see Thurian 117 (1992) 727
Hoffmann, A., see Fricke 117 (1992) 783
Hoffmann, A., see Broser 117 (1992) 788
Hoffmann, H., see Waldmann 117 (1992) 715
Hofmann, D.M., see Meyer 117 (1992) 656
Hogg, J.H.C., see Ashenford 117 (1992) 233
Hogg, J.H.C., see Jackson 117 (1992) 867
Hommel, D., W. Busse, H.-E. Gumlich, D. Suisky and J. Röseler, Energy transfer processes in rare earth doped ZnS under non-linear excitation 117 (1992) 721
Homyonfer, M., H.-H. Strehblow, W. Giriat and R. Tenne, Gettering deep bandgap impurities from semiconductors using resonance excitation photoelectrochemical etching: Fe from $Cd_{0.98}Fe_{0.02}Se$ 117 (1992) 1080
Hosomi, S., see Sohn 117 (1992) 907
Hosomi, S., see Noma 117 (1992) 1030
Hricovini, K., see Marbeuf 117 (1992) 197
Hu, Y.Z., see Koch 117 (1992) 592
Hua, G.C., see Xie 117 (1992) 1079
Humenberger, J., see Enichlmair 117 (1992) 844
Humenberger, J., see Lang 117 (1992) 954
Hunter, J.J., see Wallace 117 (1992) 320
Hvam, J.M., see Pantke 117 (1992) 763
Hvam, J.M., V.G. Lyssenko and H. Schwab, Photon echo, dephasing and recombination of bound excitons in CdSe 117 (1992) 773
Hvam, J.M., see Schwab 117 (1992) 778
Hyun, D.G., S.Y. Lee, S.H. Sohn and Y. Hamakawa, Anion vacancy states in insulator/CaS and insulator/SrS interfaces 117 (1992) 587
Hyun, D.G., see Sohn 117 (1992) 907

Ichihashi, T., see Kawano 117 (1992) 171
Ichimura, M., T. Wada, Sz. Fujita and Sg. Fujita, Reduction of compensating defects in ZnSe and ZnS by photo-irradiation 117 (1992) 689
Ichino, K., Y. Wu, Y. Kawakami, Sz. Fujita and Sg. Fujita, Fabrication of ZnCdSSe alloys by MOMBE and their applications for double-hetero and quantum-well structures 117 (1992) 527
Ichizono, K., see Shigenaka 117 (1992) 37
Ichizono, K., see Shigenaka 117 (1992) 49
Iida, F., see Kumazaki 117 (1992) 285
Iida, S., see Kinto 117 (1992) 348
Iijima, S., see Kawano 117 (1992) 171
Ikeda, M., see Akimoto 117 (1992) 420
Imai, K., see Kumazaki 117 (1992) 285
Imai, K., see Kudlek 117 (1992) 309

Imai, K., E. Kuusisto, J. Lilja, M. Pessa, D. Suzuki, H. Ozaki, K. Kumazaki and K. Hingerl, Electrical characterization of Li-doped ZnSe grown by molecular beam epitaxy 117 (1992) 406
Inoue, K., see Minami 117 (1992) 565
Inoue, K., F. Minami, Y. Kato, K. Yoshida and K. Era, Exciton resonance of hyper-Raman and hyper-Rayleigh scatterings in II–VI compounds 117 (1992) 738
Irie, T., see Ando 117 (1992) 362
Irvine, D.J., see O'Donnell 117 (1992) 497
Ishida, A., see Fujiyasu 117 (1992) 1026
Ishii, M., see Funato 117 (1992) 543
Ishino, K., see Fujiyasu 117 (1992) 1026
Isshiki, M., see Oguri 117 (1992) 116
Isshiki, M., K.S. Park, Y. Furukawa and W. Uchida, Photoluminescence of Li-doped ZnSe single crystals 117 (1992) 410
Itoh, T., K. Shinone, N. Katagiri, M. Furumiya and T. Tezuka, Stress-induced mixing of light and heavy exciton states in thin films of CdTe and CdMnTe epitaxially grown on GaAs substrates 117 (1992) 835
Iuchi, T., see Terada 117 (1992) 54

Jackson, S., W.E. Hagston, T.J. Gregory, J. Goodwin, J.E. Nicholls, J.H.C. Hogg, B. Lunn and D.E. Ashenford, Vertical transport in CdTe/$Cd_{1-x}Mn_xTe$ superlattices incorporating extended wells 117 (1992) 867
Jain, F., see Chung 117 (1992) 1062
Jantsch, W., see Hingerl 117 (1992) 341
Jeon, H., see Ren 117 (1992) 510
Jeon, H., see Xie 117 (1992) 1079
Jiang, Xue-Lin, see Tanaka 117 (1992) 997
Jiang, Xue-Yin, see Zhang 117 (1992) 1012
Jin, Ying, see Shen 117 (1992) 470
Jones, E.D., N.M. Stewart and J.B. Mullin, The diffusion of copper in cadmium telluride 117 (1992) 244
Jones, E.D., see Aslam 117 (1992) 249
Jones, I., see Brown 117 (1992) 536
Jouneau, P.H., see Cibert 117 (1992) 424
Jouneau, P.H., see Pautrat 117 (1992) 454
Juza, P., see Hingerl 117 (1992) 341

Kakuta, J., see Matsumura 117 (1992) 129
Kallis, N., see Waag 117 (1992) 820
Kaltenegger, K., see Enichlmair 117 (1992) 844
Kamata, A., see Yoshida 117 (1992) 75
Kamata, A., H. Yoshida and T. Uemoto, Homoepitaxial growth and characterization of ZnSe on different ZnSe substrates by metalorganic vapor phase epitaxy 117 (1992) 96
Kanehisa, O., see Shiiki 117 (1992) 1035
Kanemitsu, Y., A. Yamamoto, H. Matsue, H. Nabeta, Y. Masumoto, S. Yamaga, A. Yoshikawa, K. Yamanaka, Y. Nagata and T. Koda, Residual strains and disorder in ZnSSe epitaxial films on GaAs 117 (1992) 316
Kanno, T., see Takami 117 (1992) 16
Kanno, T., see Shigenaka 117 (1992) 37
Kanno, T., see Shigenaka 117 (1992) 49
Kanno, T., see Kawano 117 (1992) 171
Kanno, T., see Oda 117 (1992) 193
Kanno, T., see Sasaki 117 (1992) 222
Katagiri, N., see Itoh 117 (1992) 835
Katayama-Yoshida, H., T. Sasaki and T. Oguchi, Theory of the self-compensation in p-type ZnSe 117 (1992) 625
Kato, T., see Matsumoto 117 (1992) 578
Kato, Y., see Minami 117 (1992) 565
Kato, Y., see Inoue 117 (1992) 738
Kavokin, A.V., see Uraltsev 117 (1992) 877
Kawaguchi, Y., see Ohki 117 (1992) 102
Kawakami, K., see Matsumoto 117 (1992) 578
Kawakami, Y., see Ichino 117 (1992) 527
Kawamura, K., see Gao 117 (1992) 983
Kawano, M., N. Oda, T. Sasaki, T. Ichihashi, S. Iijima, T. Kanno and M. Saga, Twin-formation mechanisms for HgCdTe epilayers 117 (1992) 171
Kawano, M., see Sone 117 (1992) 218
Kawano, M., see Sasaki 117 (1992) 222
Kawashima, M., see Seto 117 (1992) 271
Kawashima, M., see Zhu 117 (1992) 400
Kawazu, Z., see Takami 117 (1992) 16
Kawazu, Z., see Yasumura 117 (1992) 20
Kekelidze, N.P., see Butkhuzi 117 (1992) 366
Kenny, M.J., see Wielunski 117 (1992) 460
Kerkow, H., V.X. Quang and B. Selle, Post-range implantation damage in II–VI compounds due to electronically stimulated diffusion 117 (1992) 677
Kheng, K., see Bassani 117 (1992) 391
Khulordava, T.G., see Butkhuzi 117 (1992) 366
Khulordava, T.G., see Butkhuzi 117 (1992) 1055
Kido, G., see Nakahara 117 (1992) 830
Kinto, K., M. Yagi, K. Tanigashira, T. Yamada, H. Uchiki and S. Iida, Photoluminescence studies of p- and n-type ZnS layers grown by vapor phase epitaxy 117 (1992) 348
Klingshirn, C., see Uhrig 117 (1992) 598
Klingshirn, C., Properties of the electron–hole plasma in II–VI semiconductors 117 (1992) 753
Klingshirn, C., see Schwab 117 (1992) 778
Knoll, P., see Ullrich 117 (1992) 902
Kobayashi, H., see Tanaka 117 (1992) 997
Kobayashi, M., see Nurmikko 117 (1992) 432
Kobayashi, M., see Gao 117 (1992) 983
Kobayashi, M., see Xie 117 (1992) 1079

Kobayashi, N., see Zhang 117 (1992) 1074
Kobayashi, T., see Misawa 117 (1992) 617
Koch, S.W., Y.Z. Hu, B. Fluegel and N. Peyghambarian, Coulomb effects and optical properties of semiconductor quantum dots 117 (1992) 592
Koch, S.W., see Masumoto 117 (1992) 732
Kochereshko, V.P., see Uraltsev 117 (1992) 877
Koda, T., see Kanemitsu 117 (1992) 316
Kokubo, N., see Matsumoto 117 (1992) 578
Kolenda, J., see Woggon 117 (1992) 608
Kolodziejczyk, M., Th. Filz, A. Krost, W. Richter and D.R.T. Zahn, The likelihood of III_2–VI_3 compound formation during epitaxial growth of II–VI on III–V semiconductors 117 (1992) 549
Konagai, M., see Takemura 117 (1992) 144
Kondo, A., see Takahashi 117 (1992) 979
Konishi, R., K. Noda, H. Harada and H. Sasakura, The preparation of transparent ZnO:Al thin films 117 (1992) 939
Köpp, Th., see Heimbrodt 117 (1992) 859
Köpp, Th., see Goede 117 (1992) 886
Kornack, J., see Woggon 117 (1992) 608
Kosyachenko, L.A., V.P. Makhniy, V.Ye. Baranyuk and V.V. Melnik, Optoelectronic properties of diode heterostructures based on ZnS and ZnSe 117 (1992) 583
Kotljarevsky, M.B., see Butkhuzi 117 (1992) 1055
Koyama, T., S. Ohtsuka, H. Nagata and S. Tanaka, Fabrication of microcrystallites of II–VI compound semiconductors by laser ablation method 117 (1992) 156
Koyanagi, T., see Anno 117 (1992) 816
Kozlowsky, V.I., see Nasibov 117 (1992) 1040
Kraus, M.M., see Waag 117 (1992) 820
Krawczyk, S.K., see Triboulet 117 (1992) 227
Krenn, H., see Enichlmair 117 (1992) 844
Krost, A., see Kolodziejczyk 117 (1992) 549
Kudlek, G., N. Presser, J. Gutowski, K. Hingerl, E. Abramof, A. Pesek, H. Pauli and H. Sitter, Impurity and defect distribution in ZnTe/GaAs epilayers of different thickness 117 (1992) 290
Kudlek, G., N. Presser, U.W. Pohl, J. Gutowski, J. Lilja, E. Kuusisto, K. Imai, M. Pessa, K. Hingerl and H. Sitter, Exciton complexes in ZnSe layers: a tool for probing the strain distribution 117 (1992) 309
Kuhn, B., W. Ossau, A. Waag, R.N. Bicknell-Tassius and B. Landwehr, Excited exciton states in CdTe/(CdMn)Te quantum wells 117 (1992) 871
Kuhn, T.A., W. Ossau, A. Waag, R.N. Bicknell-Tassius and G. Landwehr, Evidence of a deep donor in CdTe 117 (1992) 660
Kuhn, T.A., see Waag 117 (1992) 820
Kuhn, W., see Bauer 117 (1992) 297
Kuhn, W., see Wagner 117 (1992) 303
Kumar, V., see Hartley 117 (1992) 166
Kumazaki, K., F. Iida, K. Ohno, K. Hatano and K. Imai, Lattice strain near interface of MBE-grown ZnTe on GaAs 117 (1992) 285
Kumazaki, K., see Imai 117 (1992) 406
Kun, Z.K., D. Leksell and G.B. Brandt, Crystal growth aspects of the fabrication of high output thin film electroluminescent Edge Emitter™ arrays 117 (1992) 987
Kuroda, Y., see Suemune 117 (1992) 1068
Kuusisto, E., see Kudlek 117 (1992) 309
Kuusisto, E., see Imai 117 (1992) 406
Kuwabara, H., see Tatsuoka 117 (1992) 554
Kuwata-Gonokami, M., see Saiki 117 (1992) 802
Kuzmin, V.D., see Sabinina 117 (1992) 238

Lacis, I., see Uhrig 117 (1992) 598
Laks, D.B., see Van de Walle 117 (1992) 704
Landwehr, G., see Kuhn 117 (1992) 660
Landwehr, G., see Waag 117 (1992) 820
Landwehr, G., see Yakovlev 117 (1992) 854
Landwehr, G., see Kuhn 117 (1992) 871
Landwehr, G., see Uraltsev 117 (1992) 877
Lang, M., see Hingerl 117 (1992) 341
Lang, M., J. Humenberger, K.H. Gresslehner and K. Lischka, Tunneling in metal–insulator–semiconductor structures on epitaxially grown p-type $Hg_{1-x}Cd_xTe$ 117 (1992) 954
Lankes, S., see Wagner 117 (1992) 303
Lavallard, P., see Chamarro 117 (1992) 614
Lawson-Jack, S., see Brown 117 (1992) 536
Lee, C.D., B.H. Lim, C. Lim, H.L. Park, C.H. Chung and S.K. Chang, Growth of ZnSe on (100) GaAs by atomic layer epitaxy 117 (1992) 148
Lee, C.D., see Chang 117 (1992) 793
Lee, J.B., see Hartley 117 (1992) 166
Lee, S.Y., see Hyun 117 (1992) 587
Lei Gang, see Xu 117 (1992) 935
Leising, G., see Ullrich 117 (1992) 902
Leising, G., see Ullrich 117 (1992) 925
Leksell, D., see Kun 117 (1992) 987
Lemoine, D., see Benhlal 117 (1992) 281
Li, Jie, see Shen 117 (1992) 470
Lilja, J., see Kudlek 117 (1992) 309
Lilja, J., see Hingerl 117 (1992) 341
Lilja, J., see Imai 117 (1992) 406
Lim, B.H., see Lee 117 (1992) 148
Lim, C., see Lee 117 (1992) 148
Link, P., see Wagner 117 (1992) 303
Lischka, K., see Schmidt 117 (1992) 748
Lischka, K., see Lang 117 (1992) 954
Liu, Y.X., Y. Rajakarunanayake and T.C. McGill, Excitons in II–VI heterostructures 117 (1992) 742

Liu, Y.X., M.W. Wang, J.O. McCaldin and T.C. McGill, Proposal for the formation of a minority carrier injecting contact on wide bandgap semiconductors 117 (1992) 913
Liu, Y.X., see Phillips 117 (1992) 1050
Liu Zu-Gang, see Zhang 117 (1992) 1012
Lo, S., see Ullrich 117 (1992) 902
Loginov, Y.Y., P.D. Brown, K. Durose, N. Thompson, A.A. Alnajjar, A.W. Brinkman and J. Woods, Transmission electron microscopic studies of n- and p-type doped CdTe 117 (1992) 259
Loginov, Y.Y., see Brown 117 (1992) 536
Loginov, Y.Y., P.D. Brown, N. Thompson and K. Durose, Transmission electron microscopic study of defect formation within II–VI compounds irradiated with 100 keV electrons 117 (1992) 682
Lummer, B., see Hoffmann 117 (1992) 640
Lummer, B., see Broser 117 (1992) 788
Lunn, B., see Ashenford 117 (1992) 233
Lunn, B., see Heimbrodt 117 (1992) 859
Lunn, B., see Jackson 117 (1992) 867
Lunn, B., see Goede 117 (1992) 886
Lyssenko, V.G., see Hvam 117 (1992) 773
Lyssenko, V.G., see Schwab 117 (1992) 778

Mach, R., see Müller 117 (1992) 948
Mach, R., G.U. Reinsperger, G.O. Müller, B. Selle and G. Matzkeit, ZnS:Te, a blue electroluminescence emitter? 117 (1992) 1002
Maejima, Y., see Oda 117 (1992) 193
Magnea, N., see Bassani 117 (1992) 391
Magnea, N., see Pautrat 117 (1992) 454
Magnea, N., see Bleuse 117 (1992) 1046
Mahnke, H.-E., see Waldmann 117 (1992) 715
Makhniy, V.P., see Kosyachenko 117 (1992) 583
Mallard, R., see Cibert 117 (1992) 424
Marbeuf, A., R. Druilhe, R. Triboulet and G. Patriarche, Thermodynamic analysis of Zn–Cd–Te, Zn–Hg–Te and Cd–Hg–Te: phase separation in $Zn_xCd_{1-x}Te$ and in $Zn_xHg_{1-x}Te$ 117 (1992) 10
Marbeuf, A., D. Ballutaud, P. Martin, R. Triboulet, Y. Marfaing, J.E. Bonnet, K. Hricovini and R. Pinchaux, Angle-resolved photoemission study of $Zn_{0.15}Hg_{0.85}Te$: valence band determination 117 (1992) 197
Marfaing, Y., see Marbeuf 117 (1992) 197
Mariette, H., see Pautrat 117 (1992) 454
Mariette, H., see Bleuse 117 (1992) 1046
Marqueton, Y., see Benhlal 117 (1992) 281
Marquardt, K., see Heuken 117 (1992) 336
Marquardt, K., see Guimarães 117 (1992) 1075
Marshall, T., see Olego 117 (1992) 324
Martin, P., see Marbeuf 117 (1992) 197
Maruyama, K., see Ueda 117 (1992) 266
Masa, Y., see Seto 117 (1992) 271
Mason, S., see Arterton 117 (1992) 1008
Masumoto, Y., see Kanemitsu 117 (1992) 316
Masumoto, Y., see Yamada 117 (1992) 484
Masumoto, Y., see Yamamoto 117 (1992) 488
Masumoto, Y., B. Fluegel, K. Meissner, S.W. Koch, R. Binder, A. Paul and N. Peyghambarian, Band-gap renormalization and optical gain formation in highly excited CdSe 117 (1992) 732
Masumoto, Y., see Sasaki 117 (1992) 768
Matsubara, K., see Anno 117 (1992) 816
Matsue, H., see Kanemitsu 117 (1992) 316
Matsumoto, T., N. Kokubo, K. Kawakami and T. Kato, Capacitance–voltage characterization of n-ZnSe/n-GaAs heterojunctions 117 (1992) 578
Matsumura, N., K. Senga, J. Kakuta and J. Saraie, Reflection high energy electron diffraction study on adatom desorption from ZnSe surface under electron beam irradiation and light irradiation 117 (1992) 129
Matsushima, Y., K. Yoshino, Y. Yamamoto, S.R. Tiong and M. Hiramatsu, The band profile of zinc sulfoselenide single crystals grown by sublimation method 117 (1992) 328
Matzkeit, G., see Mach 117 (1992) 1002
Mauch, R.H., K.O. Velthaus, G. Bilger and H.W. Schock, High efficiency SrS,SrSe:$CeCl_3$ based thin film electroluminescent devices 117 (1992) 964
McCaldin, J.O., see Liu 117 (1992) 913
McCaldin, J.O., see Phillips 117 (1992) 1050
McGill, T.C., see Liu 117 (1992) 742
McGill, T.C., see Liu 117 (1992) 913
McGill, T.C., see Phillips 117 (1992) 1050
McQueen, A.E.D., see Bell 117 (1992) 58
Meissner, K., see Masumoto 117 (1992) 732
Meissner, K., see Sasaki 117 (1992) 768
Melnik, V.V., see Kosyachenko 117 (1992) 583
Meyer, B.K., W. Stadler, D.M. Hofmann, P. Omling, D. Sinerius and K.W. Benz, On the nature of the deep 1.4 eV emission bands in CdTe – a study with photoluminescence and ODMR spectroscopy 117 (1992) 656
Mikami, A., K. Terada, M. Yoshida and S. Nakajima, Chemical vapor deposition of ZnS:Tb electroluminescent films in a by-pass-HCl flow system 117 (1992) 991
Minami, F., Y. Kato, K. Yoshida, K. Inoue and K. Era, Estimation of misfit strain in epitaxially grown ZnSe/GaAs with two-photon absorption spectroscopy 117 (1992) 565
Minami, F., see Inoue 117 (1992) 738
Minami, T., H. Sato, K. Ohashi, T. Tomofuji and S. Takata, Conduction mechanism of

highly conductive and transparent zinc oxide thin films prepared by magnetron sputtering 117 (1992) 370
Minami, T., see Miyata 117 (1992) 1021
Min'kov, G.M., see Germanenko 117 (1992) 850
Misawa, K., H. Yao, T. Hayashi and T. Kobayashi, Superradiative emission from CdS microcrystallites 117 (1992) 617
Mishina, T., see Sasaki 117 (1992) 768
Mita, J., see Gao 117 (1992) 983
Mitsui, K., see Takami 117 (1992) 16
Mitsuyu, T., see Ohkawa 117 (1992) 375
Mitsuyu, T., see Saiki 117 (1992) 802
Miura, N., see Takeyama 117 (1992) 1081
Miya, T., see Ando 117 (1992) 362
Miyajima, T., see Okuyama 117 (1992) 139
Miyajima, T., H. Okuyama, K. Akimoto, Y. Mori, L. Wei and S. Tanigawa, Observation of point defects in ZnSe using the positron annihilation method 117 (1992) 694
Miyajima, T., see Nakano 117 (1992) 797
Miyamoto, Y., see Tanaka 117 (1992) 24
Miyata, T., T. Minami and S. Takata, Influence of Mn doping conditions on electroluminescent characteristics of ZnS:Mn thin-film electroluminescent (TFEL) devices using insulating ceramic 117 (1992) 1021
Mizuguchi, K., see Takami 117 (1992) 16
Mogi, I., see Nakahara 117 (1992) 830
Möllmann, K.-P., see Herrmann 117 (1992) 758
Monterrat, E., see Pautrat 117 (1992) 454
Mori, H., see Zhu 117 (1992) 400
Mori, Y., see Akimoto 117 (1992) 420
Mori, Y., see Miyajima 117 (1992) 694
Morimoto, K., Effects of hydrides of the group V elements on the growth of ZnSe by metalorganic chemical vapor deposition 117 (1992) 111
Morimoto, S., see Tanaka 117 (1992) 997
Morris, G.C., S.K. Das and P.G. Tanner, Some factors affecting efficiencies of n-CdS/p-CdTe thin film solar cells 117 (1992) 929
Müller, G.O., R. Mach, G.U. Reinsperger, E. Halden and G. Schulz, High-field electron transport in wide-gap II–VI compounds investigated by vacuum emission 117 (1992) 948
Müller, G.O., see Mach 117 (1992) 1002
Müller, M., see Woggon 117 (1992) 608
Mullin, J.B., see Jones 117 (1992) 244
Mullin, J.B., see Aslam 117 (1992) 249
Mullins, J.T. and T. Taguchi, Non-linear optical properties of the $Cd_{1-x}Zn_xS$: $Cd_{1-y}Zn_yS$ strained-layer superlattice system 117 (1992) 501
Mullins, J.T., see Brown 117 (1992) 536
Murakami, S., see Takigawa 117 (1992) 28
Murakami, S., Y. Sakachi, H. Nishino, T. Saito, K. Shinohara and T. Takigawa, Compositional profile of HgCdTe in metalorganic chemical vapor deposition (MOCVD) system with multinozzles 117 (1992) 33
Murakami, T., see Yasumura 117 (1992) 20
Murakami, T., see Takada 117 (1992) 44
Muranevich, E., see Galun 117 (1992) 666
Muranoi, T., p–n Junction diodes prepared in vapor-phase epitaxial ZnSe films using metallic Zn and Se 117 (1992) 1059
Murawala, P.A., see Funato 117 (1992) 543
Murotani, T., see Takami 117 (1992) 16

Nabeta, H., see Kanemitsu 117 (1992) 316
Nagao, Y., see Nishimura 117 (1992) 119
Nagata, H., see Koyama 117 (1992) 156
Nagata, Y., see Kanemitsu 117 (1992) 316
Nakahara, J., T. Nouchi, H. Arai, I. Mogi, G. Kido and J. Watanabe, Magneto-photoluminescence in $Cd_{1-x}Mn_xTe$ 117 (1992) 830
Nakajima, S., see Mikami 117 (1992) 991
Nakamura, A., see Tokizaki 117 (1992) 603
Nakamura, M., see Suzuki 117 (1992) 881
Nakanishi, H., see Takemura 117 (1992) 144
Nakanishi, H., see Ando 117 (1992) 362
Nakanishi, K., see Suemune 117 (1992) 1068
Nakanishi, Y., see Tatsuoka 117 (1992) 554
Nakano, K., see Okuyama 117 (1992) 139
Nakano, K., P.J. Boyce, J.J. Davies and D. Wolverson, Raman studies of phosphorus-doped ZnSe 117 (1992) 331
Nakano, K., H. Okuyama, T. Miyajima and K. Akimoto, Polarization of I_2 emission in ZnSe epitaxial layers on (100) GaAs 117 (1992) 797
Nakata, Y., see Yoshida 117 (1992) 75
Nakazawa, E., see Okamoto 117 (1992) 943
Narusawa, T., see Yokogawa 117 (1992) 480
Nasibov, A.S., V.I. Kozlowsky, P.V. Reznikov, Ya.K. Skasyrsky and Yu.M. Popov, Full color TV projector based on A_2B_6 electron-beam pumped semiconductor lasers 117 (1992) 1040
Negrii, V.D., Dynamic and optical properties of screw dislocations introduced by plastic deformation of CdS crystals at 77–4.2 K 117 (1992) 672
Neukirch, U., see Fricke 117 (1992) 783
Neumark, G.F., see Van de Walle 117 (1992) 704
Neuroth, N., see Uhrig 117 (1992) 598
Nicholls, J.E., see Dhese 117 (1992) 91
Nicholls, J.E., see Jackson 117 (1992) 867
Nishimura, K., K. Sakai, Y. Nagao and T. Ezaki, Low temperature metalorganic vapor phase epitaxial growth of $Cd_xZn_{1-x}S$ on GaAs 117 (1992) 119
Nishino, H., see Takigawa 117 (1992) 28

Nishino, H., see Murakami 117 (1992) 33
Noakes, T.C.Q., see Aslam 117 (1992) 249
Noda, K., see Konishi 117 (1992) 939
Noma, H., see Suzuki 117 (1992) 881
Noma, M., see Sohn 117 (1992) 907
Noma, M., S. Hosomi, S.H. Sohn and Y. Hamakawa, An effect of oxygen content on ZnS:TbOF green color thin film electroluminescent devices prepared by electron-beam evaporation method 117 (1992) 1030
Nouchi, T., see Nakahara 117 (1992) 830
Nunoshita, M., see Yasumura 117 (1992) 20
Nunoshita, M., see Takada 117 (1992) 44
Nurmikko, A.V., R.L. Gunshor and M. Kobayashi, Optical properties and device prospects of ZnSe-based quantum structures 117 (1992) 432
Nurmikko, A.V., see Ren 117 (1992) 510
Nurmikko, A.V., see Xie 117 (1992) 1079

Oda, N., see Kawano 117 (1992) 171
Oda, N., T. Kanno, M. Saga, R. Oikawa and Y. Maejima, Composition characterization methods for HgCdTe epilayers grown by molecular beam epitaxy 117 (1992) 193
Oda, N., see Sone 117 (1992) 218
Oda, N., see Sasaki 117 (1992) 222
O'Donnell, K.P., see Parbrook 117 (1992) 492
O'Donnell, K.P., P.J. Parbrook, F. Yang, X. Chen, D.J. Irvine, C. Trager-Cowan, B. Henderson, P.J. Wright and B. Cockayne, The optical properties of wide bandgap binary II–VI superlattices 117 (1992) 497
O'Donnell, K.P., see Trager-Cowan 117 (1992) 532
O'Donnell, K.P., Y. Fujii, P.J. Parbrook and I. Suemune, Are localized excitons responsible for lasing in disordered short period II–VI strained layer superlattices? 117 (1992) 1077
Oguchi, T., see Katayama-Yoshida 117 (1992) 625
Oguri, H., K.S. Park, M. Isshiki and Y. Furukawa, Growth of $ZnSe_{1-x}Te_x$ thin films by metalorganic chemical vapour deposition 117 (1992) 116
Ohashi, K., see Minami 117 (1992) 370
Ohishi, M., H. Saito, M. Yoneta and Y. Fujisaki, Low temperature growth of ZnSe/GaAs using hot molecular beams 117 (1992) 125
Ohkawa, K., A. Ueno and T. Mitsuyu, Molecular-beam epitaxial growth of p- and n-type ZnSe homoepitaxial layers 117 (1992) 375
Ohkawa, K., see Saiki 117 (1992) 802
Ohki, A., Y. Kawaguchi, K. Ando and S. Zembutsu, Metalorganic vapor phase epitaxy growth of ZnSe films using argon carrier gas 117 (1992) 102
Ohki, A., see Ando 117 (1992) 560
Ohnishi, T., see Oka 117 (1992) 840
Ohno, K., see Kumazaki 117 (1992) 285
Ohtsuka, S., see Koyama 117 (1992) 156
Oikawa, R., see Oda 117 (1992) 193
Oka, Y., T. Ohnishi, H. Sato and I. Souma, Spin correlation and dynamics of excitons in $Cd_{1-x}Mn_xTe$, $Cd_{1-x}Mn_xSe$ and $Cd_{1-x}Co_xSe$ 117 (1992) 840
Oka, Y., see Suzuki 117 (1992) 881
Okada, M., see Ekawa 117 (1992) 254
Okada, T., see Ando 117 (1992) 362
Okajima, M. and T. Tohda, Heteroepitaxial growth of MnS on GaAs substrates 117 (1992) 810
Okamoto, S., E. Nakazawa and T. Suzuki, Single insulating thin-film cold cathode using hot electrons in II–IV compounds 117 (1992) 943
Okamoto, T., see Yoshikawa 117 (1992) 107
Okumura, H., see Cibert 117 (1992) 424
Okuyama, H., K. Nakano, T. Miyajima and K. Akimoto, Epitaxial growth of Zn MgSSe on GaAs substrate by molecular beam epitaxy 117 (1992) 139
Okuyama, H., see Akimoto 117 (1992) 420
Okuyama, H., see Miyajima 117 (1992) 694
Okuyama, H., see Nakano 117 (1992) 797
Olego, D.J., J. Petruzzello, T. Marshall and D. Cammack, Spectroscopy of bound and free holes in p-type ZnSe layers 117 (1992) 324
Omino, A. and T. Suzuki, Bridgman growth of ZnSe crystals with a PBN crucible sealed in a molybdenum capsule 117 (1992) 80
Omling, P., see Meyer 117 (1992) 656
Ono, Y.A., see Ando 117 (1992) 969
Orders, P.J., see Hartley 117 (1992) 166
Ossau, W., see Kuhn 117 (1992) 660
Ossau, W., see Waag 117 (1992) 820
Ossau, W., see Yakovlev 117 (1992) 854
Ossau, W., see Kuhn 117 (1992) 871
Otsuka, N., see Xie 117 (1992) 1079
Ozaki, H., see Imai 117 (1992) 406
Ozaki, K., see Tanaka 117 (1992) 24

Pagés, O., M.A. Renucci, O. Briot, T. Cloitre and R.L. Aulombard, Depth profiling of carriers in ZnSe/GaAs heterostructures by Raman spectroscopy 117 (1992) 569
Pain, G.N., see Wielunski 117 (1992) 460
Pakalnis, S., see Baltramiejūnas 117 (1992) 622
Palfrey, H.D., see Archer 117 (1992) 177
Palmer, J., see Ando 117 (1992) 560
Pantelides, S.T., see Van de Walle 117 (1992) 704
Pantke, K.-H., J. Erland and J.M. Hvam, Picosecond spectroscopy of exciton–biexciton transitions in CdSe 117 (1992) 763
Parbrook, P.J., B. Henderson, K.P. O'Donnell, P.J. Wright and B. Cockayne, Criti-

cal thickness of common-anion II–VI strained layer superlattices (SLSs) 117 (1992) 492
Parbrook, P.J., see O'Donnell 117 (1992) 497
Parbrook, P.J., see Trager-Cowan 117 (1992) 532
Parbrook, P.J., see O'Donnell 117 (1992) 1077
Park, H.L., see Lee 117 (1992) 148
Park, H.L., see Chang 117 (1992) 793
Park, K.S., see Oguri 117 (1992) 116
Park, K.S., see Isshiki 117 (1992) 410
Patriarche, G., see Marbeuf 117 (1992) 10
Patterson, I.P., see Armitage 117 (1992) 1082
Paul, A., see Masumoto 117 (1992) 732
Pauli, H., see Kudlek 117 (1992) 290
Pautrat, J.L., E. Monterrat, L. Ulmer, N. Magnea, H. Mariette, J. Bleuse and P.H. Jouneau, Band gap engineering in II–VI based heterostructures 117 (1992) 454
Pautrat, J.L., see Bleuse 117 (1992) 1046
Peisach, M., see Galun 117 (1992) 666
Pelletier, C.M., see Granger 117 (1992) 203
Perkowitz, S., see Dubowski 117 (1992) 862
Perls, H., see Broser 117 (1992) 788
Pesek, A., see Kudlek 117 (1992) 290
Pessa, M., see Kudlek 117 (1992) 309
Pessa, M., see Hingerl 117 (1992) 341
Pessa, M., see Imai 117 (1992) 406
Peter, G., see Dubowski 117 (1992) 862
Peter, L.M., see Berlouis 117 (1992) 918
Petrauskas, M., see Woggon 117 (1992) 608
Petruzello, J., see Olego 117 (1992) 324
Peyghambarian, N., see Koch 117 (1992) 592
Peyghambarian, N., see Masumoto 117 (1992) 732
Peyghambarian, N., see Sasaki 117 (1992) 768
Phillips, M.C., J.F. Swenberg, Y.X. Liu, M.W. Wang, J.O. McCaldin and T.C. McGill, Forming of Al-doped ZnTe epilayers grown by molecular beam epitaxy 117 (1992) 1050
Piao, Z.S., see Shen 117 (1992) 519
Pier, Th., see Heimbrodt 117 (1992) 859
Pinchaux, R., see Marbeuf 117 (1992) 197
Podlowski, L., A. Hoffmann and I. Broser, Calorimetric absorption spectroscopy at mK temperatures – an extremely sensitive method to determine nonradiative processes in solids 117 (1992) 698
Pohl, U.W., see Kudlek 117 (1992) 309
Pohl, U.W., see Waldmann 117 (1992) 715
Pohlmann, A., see Yakovlev 117 (1992) 854
Popov, Yu.M., see Nasibov 117 (1992) 1040
Pozina, G.R., see Uraltsev 117 (1992) 877
Presser, N., see Kudlek 117 (1992) 290
Presser, N., see Kudlek 117 (1992) 309
Pressl, M., see Ullrich 117 (1992) 902
Prior, K.A., see Simpson 117 (1992) 134
Prior, K.A., see Wallace 117 (1992) 320
Pronin, A.N., see Gruzintsev 117 (1992) 975
Qiu, J., see DePuydt 117 (1992) 1078
Quang, V.X., see Kerkow 117 (1992) 677

Raisanen, A., see Vanzetti 117 (1992) 573
Rajakarunanayake, Y., see Liu 117 (1992) 742
Ray, B., see Viney 117 (1992) 806
Ray, B., see Arterton 117 (1992) 1008
Rees, D., see Hartley 117 (1992) 166
Reinsperger, G.U., see Müller 117 (1992) 948
Reinsperger, G.U., see Mach 117 (1992) 1002
Remitz, K., see Uhrig 117 (1992) 598
Ren, J., K.A. Bowers, R.P. Vaudo, J.W. Cook, Jr., J.F. Schetzina, J. Ding, H. Jeon and A.V. Nurmikko, Properties of ZnSe–$ZnSe_{0.9}Te_{0.1}$ and ZnSe–$Zn_{0.9}Cd_{0.1}Se$ multilayers 117 (1992) 510
Renucci, M.A., see Pagés 117 (1992) 569
Reznikov, P.V., see Nasibov 117 (1992) 1040
Richter, W., see Kolodziejczyk 117 (1992) 549
Rivera-Iratchet, J., see Vogel 117 (1992) 710
Rolland, S., see Bagot 117 (1992) 189
Rolland, S., R. Granger and R. Triboulet, p-to-n conversion in $Hg_{1-x}Zn_xTe$ by ion beam milling effect 117 (1992) 208
Röseler, J., see Hommel 117 (1992) 721
Rosenauer, A., see Bauer 117 (1992) 297
Roth, A.P., see Dubowski 117 (1992) 862
Roth, M., see Azoulay 117 (1992) 276
Roth, S., see Ullrich 117 (1992) 902
Roth, S., see Ullrich 117 (1992) 925
Rothemund, W., see Hingerl 117 (1992) 341
Rotter, S., see Azoulay 117 (1992) 276
Rückmann, I., see Woggon 117 (1992) 608
Rut, O.E., see Germanenko 117 (1992) 850

Sabinina, I.V., A.K. Gutakovsky, Yu.G. Sidorov, S.A. Dvoretsky and V.D. Kuzmin, Defect formation during growth of CdTe(111) and HgCdTe films by molecular beam epitaxy 117 (1992) 238
Saga, M., see Takami 117 (1992) 16
Saga, M., see Shigenaka 117 (1992) 37
Saga, M., see Shigenaka 117 (1992) 49
Saga, M., see Kawano 117 (1992) 171
Saga, M., see Oda 117 (1992) 193
Saga, M., see Sasaki 117 (1992) 222
Saiki, T., K. Takeuchi, M. Kuwata-Gonokami, T. Mitsuyu and K. Ohkawa, Giant excitonic optical nonlinearity in ZnSe grown by molecular beam epitaxy 117 (1992) 802
Saito, H., see Ohishi 117 (1992) 125
Saito, T., see Takigawa 117 (1992) 28
Saito, T., see Murakami 117 (1992) 33
Saito, T., see Sugiyama 117 (1992) 161
Saji, M., see Ekawa 117 (1992) 254
Sakachi, Y., see Murakami 117 (1992) 33

Sakai, K., see Nishimura 117 (1992) 119
Saminadayar, K., see Bassani 117 (1992) 391
Saminadayar, K., see Cibert 117 (1992) 424
Saraie, J., see Matsumura 117 (1992) 129
Sasaki, F., T. Mishina, Y. Masumoto, B. Fluegel, K. Meissner and N. Peyghambarian, Femtosecond optical nonlinearities under resonant excitation of excitons in CdSe 117 (1992) 768
Sasaki, T., see Kawano 117 (1992) 171
Sasaki, T., see Sone 117 (1992) 218
Sasaki, T., N. Oda, M. Kawano, S. Sone, T. Kanno and M. Saga, Mercury annealing effect on the electrical properties of HgCdTe grown by molecular beam epitaxy 117 (1992) 222
Sasaki, T., see Katayama-Yoshida 117 (1992) 625
Sasakura, H., see Konishi 117 (1992) 939
Sato, H., see Minami 117 (1992) 370
Sato, H., see Oka 117 (1992) 840
Sato, K., see Sawada 117 (1992) 826
Sawada, T., Y. Takada and K. Sato, Growth technique and optical characterization of (Cd,Mn)Te for fiber-optic magnetic field sensors 117 (1992) 826
Schetzina, J.F., see Ren 117 (1992) 510
Schmeusser, S., see Waag 117 (1992) 820
Schmeusser, S., see Yakovlev 117 (1992) 854
Schmidt, T., G. Daniel and K. Lischka, The excitation power dependence of the near band edge photoluminescence of II–VI semiconductors 117 (1992) 748
Schmied, B., see Waag 117 (1992) 820
Schmolke, R., E. Schöll and J. Gutowski, A model for impurity-related optical bistability in II–VI semiconductors 117 (1992) 650
Schock, H.W., see Mauch 117 (1992) 964
Schöll, E., see Schmolke 117 (1992) 650
Schulz, G., see Müller 117 (1992) 948
Schwab, H., see Hvam 117 (1992) 773
Schwab, H., V.G. Lyssenko, J.M. Hvam, M. Urban and C. Klingshirn, Dephasing and energy relaxation of localized excitons in $CdS_{1-x}Se_x$ mixed crystals 117 (1992) 778
Scott, C.G., see Ashenford 117 (1992) 233
Selle, B., see Kerkow 117 (1992) 677
Selle, B., see Mach 117 (1992) 1002
Senga, K., see Matsumura 117 (1992) 129
Seto, S., A. Tanaka, Y. Masa and M. Kawashima, Chlorine-related photoluminescence lines in high-resistivity Cl-doped CdTe 117 (1992) 271
Shaw, N., see Astles 117 (1992) 213
Shen, D.Z., X.W. Fan, Z.S. Piao and G.H. Fan, Picosecond optical bistability in ZnSe–ZnTe/CaF_2 multiple quantum wells at room temperature 117 (1992) 519
Shen, D.Z., see Zhang 117 (1992) 523
Shen, G., see Hartley 117 (1992) 166
Shen, Meng-Yan, Xiao-Jie Zhang, Ying Jin, Jing-Jing Wang, Shu-Lin Zhang, Jie Li and Shi-Xin Yuan, Spectroscopy in the ZnTe/CdTe multiple quantum wells 117 (1992) 470
Shibuya, K., see Takahashi 117 (1992) 979
Shigenaka, K., T. Uemoto, L. Sugiura, K. Ichizono, K. Hirahara, T. Kanno and M. Saga, $Hg_{1-x}Cd_xTe$ epitaxial layers grown by low mercury partial pressure metalorganic chemical vapor deposition and extended defect characterization 117 (1992) 37
Shigenaka, K., T. Kanno, M. Saga, T. Uemoto, L. Sugiura, K. Ichizono and K. Hirahara, Effects of mercury partial pressure on defects in HgTe epitaxial layers grown by metalorganic chemical vapor deposition 117 (1992) 49
Shiiki, M. and O. Kanehisa, Electroluminescence of zinc sulfide thin films activated with donors and acceptors 117 (1992) 1035
Shimizu, I., see Gotoh 117 (1992) 85
Shinohara, K., see Takigawa 117 (1992) 28
Shinohara, K., see Murakami 117 (1992) 33
Shinohara, K., see Sugiyama 117 (1992) 161
Shinohara, K., see Ueda 117 (1992) 266
Shinone, K., see Itoh 117 (1992) 835
Shirai, H., see Gotoh 117 (1992) 85
Sidorov, Yu.G., see Sabinina 117 (1992) 238
Simmons, M.Y., H.M. Al Allak, A.W. Brinkman and K. Durose, Electrical and optical characterisation of epitaxial ZnTe/CdTe/CdS and ZnTe/CdTe/GaAs p–i–n solar cell structures grown by metalorganic vapour phase epitaxy 117 (1992) 959
Simpson, J., S.J.A. Adams, S.Y. Wang, J.M. Wallace, K.A. Prior and B.C. Cavenett, UV laser assisted growth of molecular beam epitaxial ZnSe 117 (1992) 134
Simpson, J., see Wallace 117 (1992) 320
Sinerius, D., see Meyer 117 (1992) 656
Sitter, H., see Kudlek 117 (1992) 290
Sitter, H., see Kudlek 117 (1992) 309
Sitter, H., see Hingerl 117 (1992) 341
Skasyrsky, Ya.K., see Nasibov 117 (1992) 1040
Skorsetz, J., see Bauer 117 (1992) 297
Sohn, S.H., see Hyun 117 (1992) 587
Sohn, S.H., D.G. Hyun, M. Noma, S. Hosomi and Y. Hamakawa, Effective charges in II–VI semiconductors 117 (1992) 907
Sohn, S.H., see Noma 117 (1992) 1030
Söllner, J., see Heuken 117 (1992) 336

Söllner, J., see Guimarães 117 (1992) 1075
Sone, S., N. Oda, T. Sasaki and M. Kawano, Electron mobility in HgCdTe near the zero-band-gap grown by molecular beam epitaxy 117 (1992) 218
Sone, S., see Sasaki 117 (1992) 222
Sorba, L., see Vanzetti 117 (1992) 573
Souma, I., see Oka 117 (1992) 840
Souma, I., see Suzuki 117 (1992) 881
Speit, B., see Uhrig 117 (1992) 598
Spellmeyer, B., see Waldmann 117 (1992) 715
Stadler, W., see Meyer 117 (1992) 656
Stanley, R.P., see Doran 117 (1992) 465
Steele, T.A., see Hartley 117 (1992) 166
Stewart, H., see Wallace 117 (1992) 320
Stewart, N.M., see Jones 117 (1992) 244
Strehblow, H.-H., see Homyonfer 117 (1992) 1080
Suemune, I., K. Nakanishi, Y. Fujii, Y. Kuroda, M. Fujimoto and M. Yamanishi, Photopumped ZnSe/ZnSSe blue semiconductor lasers and a theoretical calculation of the optical gain 117 (1992) 1068
Suemune, I., see O'Donnell 117 (1992) 1077
Suemune, I., Are common-anion and common-cation heterostructures applicable as excellent II–VI laser materials? 117 (1992) 1083
Sugiura, L., see Shigenaka 117 (1992) 37
Sugiura, L., see Shigenaka 117 (1992) 49
Sugiyama, I., A. Hobbs, T. Saito, O. Ueda, K. Shinohara and H. Takigawa, Dislocation reduction in HgCdTe epilayers on GaAs by using CdTe/CdZnTe strained-layer superlattices in CdTe layers 117 (1992) 161
Sugiyama, I., see Hobbs 117 (1992) 475
Suh, E.-K., Spin-flip Raman scattering and photoluminescence in modulation doped CdTe/$Cd_{1-x}Mn_xTe$:In superlattices 117 (1992) 890
Suisky, D., see Hommel 117 (1992) 721
Suita, M., see Yasumura 117 (1992) 20
Suita, M., see Takada 117 (1992) 44
Sulzer, G., see Waldmann 117 (1992) 715
Sun Weiguo and Wang Bin, The characterization of HgCdTe passivated with native fluoride-oxide and Sb_2S_3 coating 117 (1992) 183
Suzuki, D., see Imai 117 (1992) 406
Suzuki, K., M. Nakamura, I. Souma, K. Yanata, Y. Oka, H. Fujiyasu and H. Noma, Magneto-optical properties of low-dimensional excitons in microcrystals and superlattices of $Cd_{1-x}Mn_xTe$ 117 (1992) 881
Suzuki, T., see Omino 117 (1992) 80
Suzuki, T., see Okamoto 117 (1992) 943
Sweck, J., see Bauer 117 (1992) 297
Swenberg, J.F., see Phillips 117 (1992) 1050
Świątek, K., see Godlewski 117 (1992) 634

Taguchi, T., see Yamada 117 (1992) 484
Taguchi, T., see Mullins 117 (1992) 501
Taguchi, T., see Brown 117 (1992) 536
Takada, H., see Yasumura 117 (1992) 20
Takada, H., T. Murakami, M. Suita, K. Yasumura, Y. Endo, K. Takahashi and M. Nunoshita, The growth rate of $Cd_xHg_{1-x}Te$ grown by metalorganic chemical vapor deposition 117 (1992) 44
Takada, Y., see Sawada 117 (1992) 826
Takagi, Y., see Takeyama 117 (1992) 1081
Takahashi, K., see Yasumura 117 (1992) 20
Takahashi, K., see Takada 117 (1992) 44
Takahashi, K., see Takemura 117 (1992) 144
Takahashi, K., K. Shibuya and A. Kondo, Degradation induced by the Sr^{2+} vacancies in SrS:Ce electroluminescent devices 117 (1992) 979
Takami, A., Z. Kawazu, T. Takiguchi, K. Mitsui, K. Mizuguchi, T. Murotani, K. Yasumura, T. Kanno and M. Saga, High quality p-$Cd_{0.22}Hg_{0.78}Te$ grown by liquid-phase epitaxy 117 (1992) 16
Takata, S., see Minami 117 (1992) 370
Takata, S., see Miyata 117 (1992) 1021
Takaya, M., see Tokizaki 117 (1992) 603
Takemura, Y., M. Konagai, H. Nakanishi and K. Takahashi, Self-limiting growth with 0.5 monolayer per cycle in atomic layer epitaxy of ZnTe 117 (1992) 144
Takeuchi, K., see Saiki 117 (1992) 802
Takeuchi, Y., see Fujiyasu 117 (1992) 1026
Takeyama, T., S. Adachi, Y. Takagi, N. Miura and V.F. Aguekian, Magnetic field induced exciton photoluminescence in $Cd_{1-x}Mn_xTe$ ($x = 0.15$–0.45) 117 (1992) 1081
Takigawa, H., H. Nishino, T. Saito, S. Murakami and K. Shinohara, Metalorganic chemical vapor deposition growth of CdTe on GaAs in a vertical reactor with multi-nozzles 117 (1992) 28
Takigawa, H., see Sugiyama 117 (1992) 161
Takigawa, H., see Hobbs 117 (1992) 475
Takigawa, T., see Murakami 117 (1992) 33
Takiguchi, T., see Takami 117 (1992) 16
Tamulaitis, G., see Baltramiejūnas 117 (1992) 622
Tanaka, A., see Ekawa 117 (1992) 254
Tanaka, A., see Seto 117 (1992) 271
Tanaka, M., K. Ozaki, K. Yamamoto, H. Ebe and Y. Miyamoto, Epitaxial growth of HgCdTe on sapphire for photoconductive detectors 117 (1992) 24
Tanaka, S., see Koyama 117 (1992) 156
Tanaka, S., see Yodo 117 (1992) 415
Tanaka, S., S. Morimoto, K. Yamada, H. Kobayashi, Zhi-Lin Zhang and Xue-Yin Jiang, Excitation mechanism of Tm^{3+} centers in ZnS electroluminescent thin films 117 (1992) 997
Tanigashira, K., see Kinto 117 (1992) 348

Tanigawa, S., see Miyajima 117 (1992) 694
Tanner, P.G., see Morris 117 (1992) 929
Tatarenko, S., see Bassani 117 (1992) 391
Tatarenko, S., see Cibert 117 (1992) 424
Tatsuoka, H., H. Kuwabara, Y. Nakanishi and H. Fujiyasu, New approach to the mechanism of strain release in lattice-mismatched epitaxial films 117 (1992) 554
Tenne, R., see Azoulay 117 (1992) 276
Tenne, R., see Galun 117 (1992) 666
Tenne, R., see Homyonfer 117 (1992) 1080
Terada, K., see Mikami 117 (1992) 991
Terada, T., Y. Fujita, S. Fujii and T. Iuchi, Composition control in $Hg_{1-z}Cd_zTe$ growth by photoassisted MOCVD using an excimer laser 117 (1992) 54
Tezuka, T., see Itoh 117 (1992) 835
Thompson, N., see Loginov 117 (1992) 259
Thompson, N., see Loginov 117 (1992) 682
Thurian, P., R. Heitz, A. Hoffmann and I. Broser, Nonlinear Zeeman effect of the Ni^{3+} centre in ZnO 117 (1992) 727
Tiong, S.R., see Matsushima 117 (1992) 328
Toda, T., see Hishida 117 (1992) 396
Tohda, T., see Okajima 117 (1992) 810
Tohno, S., see Ando 117 (1992) 560
Tokizaki, T., H. Akiyama, M. Takaya and A. Nakamura, Linear and nonlinear optical properties of CdS microcrystallites in glasses 117 (1992) 603
Tomm, J.W., see Herrmann 117 (1992) 758
Tomofuji, T., see Minami 117 (1992) 370
Trager-Cowan, C., see O'Donnell 117 (1992) 497
Trager-Cowan, C., P.J. Parbrook, F. Yang, X. Chen, B. Henderson, K.P. O'Donnell, B. Cockayne and P.J. Wright, Electron beam excitation and profiling of strained CdS epilayers grown by metalorganic vapour phase epitaxy on GaAs(111)A, GaAs(100), ZnSe(100) and ZnS(100) substrates 117 (1992) 532
Triboulet, R., see Marbeuf 117 (1992) 10
Triboulet, R., see Bagot 117 (1992) 189
Triboulet, R., see Marbeuf 117 (1992) 197
Triboulet, R., see Rolland 117 (1992) 208
Triboulet, R., A. Durand, P. Gall, J. Bonnafé, J.P. Fillard and S.K. Krawczyk, Qualification by optical means of CdTe substrates 117 (1992) 227
Triboulet, R., see Benhlal 117 (1992) 281
Tsuji, O., see Funato 117 (1992) 543
Tsuruoka, T., see Gao 117 (1992) 983

Uchida, W., see Isshiki 117 (1992) 410
Uchiki, H., see Kinto 117 (1992) 348
Ueda, O., see Sugiyama 117 (1992) 161
Ueda, O., K. Maruyama, A. Hobbs and K. Shinohara, Transmission electron microscopic evaluation of metalorganic chemical vapor deposition-grown CdTe crystals on sapphire substrates 117 (1992) 266
Ueda, O., see Hobbs 117 (1992) 475
Uemoto, T., see Shigenaka 117 (1992) 37
Uemoto, T., see Shigenaka 117 (1992) 49
Uemoto, T., see Kamata 117 (1992) 96
Ueno, A., see Ohkawa 117 (1992) 375
Uhrig, A., A. Wörner, C. Klingshirn, L. Banyai, S. Gaponenko, I. Lacis, N. Neuroth, B. Speit and K. Remitz, Nonlinear optical properties of semiconductor quantum dots 117 (1992) 598
Ullrich, B., Bouchenaki, S. Roth, C. Heller, G. Leising, S. Lo, M. Pressl and P. Knoll, A newly observed effect: He–Ne laser transmission modulation performed with epitaxial and sprayed thin CdS films 117 (1992) 902
Ullrich, B., C. Bouchenaki, S. Roth and G. Leising, Bistable optical device realization with thin CdS films 117 (1992) 925
Ulmer, L., see Pautrat 117 (1992) 454
Ulmer, L., see Bleuse 117 (1992) 1046
Uraltsev, I.N., see Yakovlev 117 (1992) 854
Uraltsev, I.N., V.P. Kochereshko, A.V. Kavokin, G.R. Pozina, D.R. Yakovlev, G. Langwehr, R.N. Bicknell-Tassius and A. Waag, Resonant reflectivity study of exciton oscillator strength in CdTe/(Cd, Mn)Te quantum wells and superlattices 117 (1992) 877
Urban, M., see Schwab 117 (1992) 778

Van de Walle, C.G., D.B. Laks, G.F. Neumark and S.T. Pantelides, Solubilities, defect reactions and doping limits in ZnSe 117 (1992) 704
Vanzetti, L., X. Yu, A. Raisanen, L. Sorba, G. Haugstad, G. Bratina and A. Franciosi, Engineering ZnSe–GaAs band offsets 117 (1992) 573
Varga, I.K., see Hartley 117 (1992) 166
Vaudo, R.P., see Ren 117 (1992) 510
Velthaus, K.O., see Mauch 117 (1992) 964
Verma, M., see Ashenford 117 (1992) 233
Viney, I.V.F., B. Ray, J.W. Brightwell and B. Arterton, Excitation and fluorescence spectra in $Ca_{1-x}Cd_xS$ solid solutions 117 (1992) 806
Viney, I.V.F., see Arterton 117 (1992) 1008
Vogel, E.E., M.A. de Orúe, J. Rivera-Iratchet and M.L. Flores, Application of the method of coherent states to the optical properties of Fe^{2+} in ZnSe 117 (1992) 710
Volkov, V.T., see Gruzintsev 117 (1992) 975

Waag, A., see Kuhn 117 (1992) 660

Waag, A., T.A. Kuhn, S. Schmeusser, B. Schmied, M.M. Kraus, N. Kallis, W. Ossau, R.N. Bicknell-Tassius and G. Landwehr, Photoassisted MBE growth of doped CdTe and CdMnTe thin films and their characterization 117 (1992) 820

Waag, A., see Yakovlev 117 (1992) 854

Waag, A., see Kuhn 117 (1992) 871

Waag, A., see Uraltsev 117 (1992) 877

Wada, T., see Ichimura 117 (1992) 689

Wagner, H.P., see Bauer 117 (1992) 297

Wagner, H.P., S. Lankes, K. Wolf, W. Kuhn, P. Link and W. Gebhardt, Spectroscopic investigations of donor and acceptor states in n- and p-doped ZnTe epilayers 117 (1992) 303

Waldmann, H., H.-E. Mahnke, B. Spellmeyer, G. Sulzer, W.-D. Zeitz, H. Hoffmann, H.-E. Gumlich and U. Pohl, Magnetic behavior of isolated Fe and Ni ions in II–VI compounds 117 (1992) 715

Wallace, J.M., see Simpson 117 (1992) 134

Wallace, J.M., J. Simpson, S.Y. Wang, H. Stewart, J.J. Hunter, S.J.A. Adams, K.A. Prior and B.C. Cavenett, Electrical characterization of iodine doped molecular beam epitaxial ZnSe 117 (1992) 320

Walton, J.C., see Bell 117 (1992) 58

Wang Bin, see Sun 117 (1992) 183

Wang, C., see Chu 117 (1992) 1073

Wang, Hailong, see Cui 117 (1992) 505

Wang, Jing-Jing, see Shen 117 (1992) 470

Wang, M.W., see Liu 117 (1992) 913

Wang, M.W., see Phillips 117 (1992) 1050

Wang, S.Y., see Simpson 117 (1992) 134

Wang, S.Y., see Wallace 117 (1992) 320

Wang, S.Y., see Zhang 117 (1992) 523

Watanabe, J., see Nakahara 117 (1992) 830

Watson, C.C.R., see Alnajjar 117 (1992) 385

Wei, L., see Miyajima 117 (1992) 694

Wielunski, L.S., M.J. Kenny and G.N. Pain, Analysis of HgTe/CdTe MOCVD grown superlattice epitaxial structures on GaAs by ion beam techniques 117 (1992) 460

Williams, J.O., see Zheng 117 (1992) 358

Williams, J.O., A.C. Wright and H.M. Yates, High resolution and conventional transmission electron microscopy in the characterisation of thin films and interfaces involving II–VI materials 117 (1992) 441

Williams, J.O., see Armitage 117 (1992) 1082

Willoughby, A.F.W., see Archer 117 (1992) 177

Willoughby, A.F.W., see Aslam 117 (1992) 249

Woggon, U., Rückmann, J. Kornack, M. Müller, J. Cesnulevicius, M. Petrauskas and J. Kolenda, Interface transfer processes and spectral hole burning in CdSe quantum confined clusters 117 (1992) 608

Wolf, K., see Wagner 117 (1992) 303

Wolverson, D., see Nakano 117 (1992) 331

Woods, J., see Loginov 117 (1992) 259

Wörner, A., see Uhrig 117 (1992) 598

Wright, A.C., see Williams 117 (1992) 441

Wright, P.J., see Dhese 117 (1992) 91

Wright, P.J., see Parbrook 117 (1992) 492

Wright, P.J., see O'Donnell 117 (1992) 497

Wright, P.J., see Trager-Cowan 117 (1992) 532

Wu, C.Q., see Chu 117 (1992) 1073

Wu, Y., see Ichino 117 (1992) 527

Xie, W., D.C. Grillo, M. Kobayashi, R.L. Gunshor, G.C. Hua, N. Otsuka, H. Jeon, J. Ding and A.V. Nurmikko, ZnSe/$Zn_{0.8}Cd_{0.2}Se$ quantum well LEDs and lasers 117 (1992) 1079

Xu Shao-Hong, see Zhang 117 (1992) 1012

Xu, Wu, Xinyi Zhang and Xurong Xu, Energy transfer from Mn to Tm ions in ZnS at high pressure 117 (1992) 718

Xu, Xurong, see Xu 117 (1992) 718

Xu Xurong, Lei Gang and Xu Zheng, Multiplication of carriers by impact ionization 117 (1992) 935

Xu Zheng, see Xu 117 (1992) 935

Yakovlev, D.R., W. Ossau, G. Landwehr, R.N. Bicknell-Tassius, A. Waag, S. Schmeusser, I.N. Uraltsev, A. Pohlmann and E.O. Göbel, Dynamics of two-dimensional exciton magnetic polaron in CdTe/(Cd,Mn)Te quantum wells 117 (1992) 854

Yakovlev, D.R., see Uraltsev 117 (1992) 877

Yagi, M., see Kinto 117 (1992) 348

Yamada, K., see Tanaka 117 (1992) 997

Yamada, T., see Kinto 117 (1992) 348

Yamada, Y., Y. Masumoto and T. Taguchi, Hydrostatic-pressure-induced type-I → type-II conversion in ZnSe-ZnS strained-layer superlattices 117 (1992) 484

Yamada, Y., see Yamamoto 117 (1992) 488

Yamaga, S. and A. Yoshikawa, Atomic layer epitaxy of ZnS by a new gas supplying system in low-pressure metalorganic vapor phase epitaxy 117 (1992) 152

Yamaga, S., see Kanemitsu 117 (1992) 316

Yamaga, S. and A. Yoshikawa, Dependence of electrical and optical properties of iodine-doped cubic ZnCdS films on solid composition 117 (1992) 353

Yamaguchi, T., see Hishida 117 (1992) 396

Yamamoto, A., see Kanemitsu 117 (1992) 316

Yamamoto, A., Y. Yamada and Y. Masumoto, New characterization method of

biaxial stress by Raman scattering: demonstration in ZnSe–ZnS strained-layer superlattices 117 (1992) 488
Yamamoto, K., see Tanaka 117 (1992) 24
Yamamoto, Y., see Matsushima 177 (1992) 328
Yamanaka, K., see Kanemitsu 117 (1992) 316
Yamanishi, M., see Suemune 117 (1992) 1068
Yanata, K., see Suzuki 117 (1992) 881
Yang, F., see O'Donnell 117 (1992) 497
Yang, F., see Trager-Cowan 117 (1992) 532
Yao, H., see Misawa 117 (1992) 617
Yao, T., see Zhu 117 (1992) 400
Yasuda, K., see Ekawa 117 (1992) 254
Yasumura, K., see Takami 117 (1992) 16
Yasumura, K., T. Murakami, M. Suita, H. Takada, K. Takahashi, M. Nunoshita and Z. Kawazu, $Cd_xHg_{1-x}Te$ double-layers grown by liquid phase epitaxy 117 (1992) 20
Yasumura, K., see Takada 117 (1992) 44
Yates, H.M., see Zheng 117 (1992) 358
Yates, H.M., see Williams 117 (1992) 441
Yates, H.M., see Armitage 117 (1992) 1082
Yodo, T. and S. Tanaka, Li^+ ion implantation into ZnS epitaxial layers grown by metalorganic vapor phase epitaxy 117 (1992) 415
Yokogawa, T. and T. Narusawa, ZnTe/ZnSTe doping superlattices grown on InP substrates by metalorganic vapor phase epitaxy 117 (1992) 480
Yoneta, M., see Ohishi 117 (1992) 125
Yoshida, H., T. Fujii, A. Kamata and Y. Nakata, Undoped ZnSe single crystal growth by the vertical Bridgman method 117 (1992) 75
Yoshida, H., see Kamata 117 (1992) 96
Yoshida, K., see Minami 117 (1992) 565
Yoshida, K., see Inoue 117 (1992) 738
Yoshida, M., see Mikami 117 (1992) 991
Yoshikawa, A. and T. Okamoto, On the mechanism of growth-rate enhancement by photocatalysis in metalorganic vapor phase epitaxy of ZnSe 117 (1992) 107
Yoshikawa, A., see Yamaga 117 (1992) 152
Yoshikawa, A., see Kanemitsu 117 (1992) 316
Yoshikawa, A., see Yamaga 117 (1992) 353
Yoshino, K., see Matsushima 117 (1992) 328
Yu, X., see Vanzetti 117 (1992) 573
Yuan, Shi-Xin, see Shen 117 (1992) 470

Zahn, D.R.T., see Kolodziejczyk 117 (1992) 549
Zeinert, A., P. Benalloul, C. Barthou, J. Benoit, J. Dreyhsig and H.-E. Gumlich, Excitation efficiency of electrons in alternating driven ZnS:Mn electroluminescent devices 117 (1992) 1016
Zeitz, W.-D., see Waldmann 117 (1992) 715
Zembutsu, S., see Ohki 117 (1992) 102
Zembutsu, S., see Ando 117 (1992) 560
Zhang, Bu-Xin, see Zhang 117 (1992) 1012
Zhang, J.H., see Guan 117 (1992) 515
Zhang, J.Y., X.W. Fan, S.Y. Wang, D.Z. Shen and G.H. Fan, Optical bistability in ZnSe–ZnS superlattices with a Fabry–Pérot cavity 117 (1992) 523
Zhang, S. and N. Kobayashi, Photoluminescence from narrow ZnSe/GaAs/ZnSe quantum wells 117 (1992) 1074
Zhang, Shu-Lin, see Shen 117 (1992) 470
Zhang, Xiao-Jie, see Shen 117 (1992) 470
Zhang, Xinyi, see Xu 117 (1992) 718
Zhang, Zhi-Lin, see Tanaka 117 (1992) 997
Zhang Zhi-Lin, Zhang Bu-Xin, Zhao Wei-Ming, Jiang Xue-Yin, Liu Zu-Gang and Xu Shao-Hong, Computer simulation of the transient process of ZnS:Mn thin film electroluminescence 117 (1992) 1012
Zhao Wei-Ming, see Zhang 117 (1992) 1012
Zheng, Jia-zhen, J.W. Allen, H.M. Yates and J.O. Williams, The M-centre in zinc selenide grown by metalorganic chemical vapour deposition 117 (1992) 358
Zhu, Z., H. Mori, M. Kawashima and T. Yao, Planar doping of p-type ZnSe layers with lithium grown by molecular beam epitaxy 117 (1992) 400

Journal of Crystal Growth 117 (1992) 1100–1103
North-Holland

JOURNAL OF CRYSTAL GROWTH

Subject index

Adducts 44, 91
Adsorption 129, 134, 238, 254, 569, 666
Apparatus
– for thin film growth
– – by hot wall epitaxy
– – – of II–VI compounds 1026
– – by sputtering
– – – of zinc oxide 939
– for miscellaneous purposes
– – measuring optical bistability 519
– – sealing crucibles by electron beam welder 80

Cadmium
– cobalt selenide 840
– manganese selenide 840
– manganese telluride 424, 820, 826, 830, 835, 840, 881, 1081
– mercury telluride 1, 16, 20, 24, 28, 33, 37, 44, 54, 161, 166, 171, 177, 183, 193, 203, 213, 218, 222, 238, 454, 460, 758, 844, 954, 1046
– selenide 492, 497, 603, 608, 732, 763, 768, 773, 1077, 1080
– selenide telluride 666
– sulphide 156, 362, 420, 492, 497, 532, 536, 617, 622, 650, 672, 698, 738, 753, 788, 902, 918, 925, 1026
– sulphoselenide 598, 614, 778, 1040
– telluride 156, 161, 227, 233, 238, 244, 249, 254, 259, 266, 271, 385, 391, 420, 424, 475, 554, 656, 660, 748, 820, 835, 854, 859, 862, 867, 871, 877, 886, 890, 929, 959, 1073
– zinc selenide 1078
– zinc sulphide 119, 501, 536
– zinc telluride 161, 276, 281, 424, 465, 475, 656, 682
Calcium
– cadmium sulphide 806
– sulphide 587, 969, 975
Characterization methods
– by absorption spectroscopy 156, 341, 432, 497, 501, 515, 523, 532, 565, 583, 592, 598, 603, 608, 614, 622, 640, 732, 758, 763, 768, 806, 816, 859, 902
– by attenuation of light 987
– by Auger electron spectroscopy 183, 634
– by calorimetric absorption spectroscopy 698
– by cathodoluminescence 341, 385, 532, 560, 943, 975
– by deep level transient spectroscopy 578
– by electrical methods 16, 20, 37, 49, 54, 102, 111, 119, 134, 183, 203, 208, 213, 218, 222, 227, 233, 254, 259, 271, 281, 320, 341, 353, 358, 366, 370, 385, 391, 396, 400, 406, 432, 480, 560, 569, 578, 583, 625, 666, 677, 689, 694, 850, 918, 925, 929, 935, 939, 943, 948, 954, 959, 969, 979, 983, 1002, 1012, 1021, 1026, 1030, 1035, 1040, 1050, 1055, 1059
– by electroluminescence 432, 510, 583, 587, 964, 969, 979, 983, 987, 991, 997, 1002, 1008, 1012, 1016, 1021, 1026, 1030, 1035, 1055, 1059, 1062, 1073, 1078, 1079, 1080
– by electron beam induced current 560, 1059
– by electron microscopy 10, 37, 49, 156, 161, 171, 238, 259, 266, 297, 441, 475, 536, 543, 554, 560, 666, 682, 826, 862, 881, 929, 1008, 1079
– by electron paramagnetic resonance 656, 727
– by electron probe microanalysis 276, 826
– by ellipsometry 166, 918
– by emission 309, 432, 454, 480, 527, 640, 718, 721, 732, 753, 758, 783, 806, 835, 840, 859, 881, 943, 964, 1062
– by ion beam techniques 460
– by interference spectra 788
– by infrared reflectivity 281
– by infrared tomography 227
– by infrared transmission 37, 166, 193, 213, 227
– by light scattering 227
– by magnetic circularly polarized emission 656
– by magnetic properties 715
– by magneto-optical properties 816, 881, 886
– by magnetophotoluminescence 830
– by magnetoreflection 835
– by mass spectrometry 80
– by nuclear magnetic resonance 58
– by optical bistability 519, 523, 650
– by optical microscopy 20, 148, 171, 238, 672, 826, 844
– by optical properties 91, 290, 505, 1068
– by particle size distribution analysis 156, 1008
– by photoemission spectroscopy 197
– by photoionization 358
– by photoluminescence 85, 102, 111, 125, 156, 227, 271, 285, 303, 328, 341, 348, 353, 362, 366, 375, 391, 396, 400, 410, 415, 420, 424, 441, 465, 470, 480, 484, 492, 497, 501, 510, 515, 519, 583, 614, 617, 634, 656, 660, 666, 672, 727, 748, 788, 793, 810, 820, 840, 854, 862, 867, 871, 890, 969, 991, 997, 1002, 1008, 1035, 1046, 1074, 1075, 1077, 1081
– by photomagnetization 844
– by photon echo 773, 778
– by radiotracer diffusion 177
– by Raman spectroscopy 285, 309, 316, 324, 331, 488, 505, 549, 569, 738, 862, 890
– by reflectance 328, 523, 835
– by reflection high energy electron diffraction 129, 166, 400, 810
– by reflection spectroscopy 877, 886
– by reflection type polarization spectroscopy 802
– by Rutherford back scattering 460

- by secondary ion mass spectrometry 54, 102, 213, 353, 391, 400, 862, 1046
- by second harmonic generation 501, 738, 894
- by thermal expansion coefficient 189
- by thermally induced bistability 925
- by X-ray methods 28, 37, 44, 85, 96, 102, 148, 156, 166, 233, 276, 290, 309, 328, 362, 370, 375, 543, 549, 565, 573, 666, 797, 806, 810, 816, 859, 964, 983, 991, 1008, 1030, 1079, 1082
- by X-ray photoelectron spectroscopy 573, 816, 964, 1080
- by Zeeman effect 727, 871, 881

Computer simulation 732, 1012, 1083
Constitutional supercooling 276

Devices 1, 16, 24, 139, 183, 193, 375, 432, 510, 523, 527, 578, 583, 587, 894, 913, 925, 929, 935, 943, 964, 969, 979, 983, 987, 997, 1008, 1012, 1016, 1021, 1026, 1030, 1035, 1040, 1050, 1055, 1059, 1062, 1068, 1073, 1078, 1079
Diffusional control 244, 249, 259, 385, 400, 460, 492, 677, 682, 806, 867
Distribution coefficient 213, 276, 913
Dopants 1, 102, 111, 119, 134, 213, 244, 249, 254, 259, 271, 290, 303, 320, 324, 331, 341, 385, 391, 406, 415, 420, 480, 510, 640, 660, 666, 694, 698, 704, 718, 721, 727, 783, 788, 806, 820, 890, 913, 935, 964, 969, 979, 987, 997, 1021, 1026, 1035, 1050, 1073, 1078, 1079

Etching
- chemical 271, 549, 666
- dry BCl_3 plasma 375
- photochemical 666, 1080

Fiber optics 826

Grain boundary 96, 1098

Heterojunction 20, 85, 316, 362, 454, 488, 497, 527, 543, 549, 560, 569, 573, 578, 583, 742, 844, 894, 954, 959, 1062, 1073, 1078, 1079, 1083

Impurity 49, 75, 80, 213, 249, 254, 290, 303, 309, 328, 336, 348, 353, 358, 410, 415, 420, 460, 625, 634, 640, 650, 660, 666, 694, 704, 710, 715, 727, 763, 773, 783, 788, 820, 850, 894, 902, 913, 918, 948, 1080
Interface 20, 166, 183, 276, 285, 316, 441, 460, 484, 488, 549, 560, 569, 578, 583, 587, 608, 742, 890, 918, 954, 1012, 1016, 1050, 1075

Kinetics
- of growth 1, 37, 44, 67, 75, 107, 116, 125, 134, 144, 152, 166, 254, 820, 991, 1088
- of interface control 560
- of luminescence decay 721
- of self-compensation 913
- of transfer processes 608

Lasers 139, 432, 527, 894, 1040, 1046, 1062, 1068, 1077, 1078, 1083
Lattice mismatch 10, 24, 139, 309, 316, 515, 527, 554, 560, 565, 578, 886

Manganese
- sulphide 810
- telluride 816

Melt growth technique
- by Bridgman–Stockbarger method
  - of cadmium cobalt selenide 840
  - of cadmium manganese selenide 840
  - of cadmium manganese telluride 826, 840
  - of cadmium selenide telluride 666
  - of cadmium telluride 660
  - of zinc chalcogenides 715
  - of zinc selenide 75, 80
- by floating zone method
  - of cadmium telluride 656
  - of cadmium zinc telluride 656
  - of mercury cadmium telluride 758
  - of mercury zinc telluride 208
- by uniaxial solidification
  - of cadmium zinc telluride 276

Mercury
- cadmium telluride 1, 16, 20, 24, 28, 33, 37, 44, 54, 161, 166, 171, 177, 183, 189, 193, 203, 213, 218, 238, 454, 460, 758, 844, 954, 1046
- manganese telluride 850
- telluride 49
- zinc telluride 189, 203, 208

Monte Carlo method 732
Morphological stability 1008
Morphology of growth 96, 148, 415, 543, 1008, 1082

Nonlinear optics 501, 519, 523, 598, 603, 622, 650, 738, 768, 773, 778, 788, 802, 894
Nucleation 598

Optoelectronics 583, 732

Perfection of crystals 16, 20, 28, 37, 49, 67, 75, 96, 119, 125, 171, 208, 227, 233, 238, 259, 266, 276, 290, 336, 366, 385, 396, 460, 492, 536, 560, 578, 656, 660, 666, 672, 677, 682, 689, 694, 704, 758, 820, 902, 929, 979, 1055
Phase diagrams 10, 991
Phenomenological theory 710, 830, 907
Polymorphism/polytypism 85, 536
Precursor 58, 119
Purification of materials 826, 1080

Quantum wells/size effects 85, 391, 424, 432, 454, 465, 470, 480, 484, 492, 501, 510, 519, 523, 527, 543, 592, 598, 603, 608, 617, 622, 742, 753, 854, 859, 862, 867, 871, 877, 881, 886, 890, 894, 954, 1026, 1046, 1062, 1068, 1074, 1075, 1077, 1078, 1079, 1083

Segregation 276
Self-diffusion
- of mercury 177

Solar cells 929, 959, 1073
Solid growth technique
– by recrystallization
– – of zinc sulphide 1008
Solubility 704
Solution growth technique
– by anodic oxidation
– – of cadmium sulphide 918
– by flux method
– – of cadmium telluride 271
– – of cadmium zinc telluride 281
– – of zinc selenide telluride 793
Strain 49, 96, 161, 233, 249, 281, 285, 290, 297, 309, 316, 336, 424, 470, 484, 488, 492, 497, 505, 515, 532, 554, 560, 565, 738, 742, 797, 835, 850, 871, 886, 1075
Strontium
– selenide 964
– sulphide 587, 943, 964, 979, 983
Superlattices 85, 161, 166, 454, 460, 470, 475, 480, 484, 488, 492, 497, 501, 505, 510, 515, 523, 536, 742, 753, 867, 877, 881, 890, 1026, 1074, 1075, 1077, 1079
Surface processes 134, 183, 666
Surface structure 96

Tellurium
– organic 58
Thermodynamics 10, 689, 704, 913
Thin film growth
– by atomic layer epitaxy
– – of zinc selenide 85, 148
– – of zinc sulphide 152
– – of zinc telluride 144
– by electrodeposition
– – of cadmium telluride 929
– by hot wall epitaxy
– – of cadmium manganese telluride 835, 881
– – of cadmium selenide 768
– – of cadmium sulphide 753, 1026
– – of cadmium telluride 161, 475, 554, 835
– – of cadmium zinc telluride 161, 475
– – of mercury cadmium telluride 844
– – of zinc telluride 290, 303
– by ionized cluster beam
– – of manganese telluride 816
– by laser ablation
– – of cadmium sulphide 156
– – of cadmium telluride 156, 862
– by liquid phase epitaxy
– – of cadmium sulphide 902, 925
– – of mercury cadmium telluride 16, 20, 24, 213
– by metalorganic molecular beam epitaxy
– – of zinc cadmium sulphoselenide 527
– by molecular beam epitaxy
– – of cadmium manganese telluride 424, 820
– – of cadmium telluride 238, 391, 424, 660, 820, 854, 859, 871, 877, 886, 890
– – of cadmium zinc selenide 1078, 1079
– – of cadmium zinc telluride 424, 465
– – of manganese sulphide 810
– – of mercury cadmium telluride 166, 171, 193, 218, 222, 238, 454, 1046
– – of zinc chalcogenides 505, 510
– – of zinc magnesium sulphoselenide 139
– – of zinc selenide 125, 129, 134, 233, 309, 320, 324, 341, 375, 400, 406, 573, 694, 797, 802, 1078, 1079
– – of zinc sulphoselenide 1078
– – of zinc telluride 285, 396, 1050
– by magnetron sputtering
– – of zinc oxide 370
– by radical beam gettering epitaxy
– – of zinc oxide 366
– by sintering
– – of cadmium sulphide 362
– by sputtering
– – of strontium sulphide 983
– – of zinc oxide 939
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of cadmium sulphide 902
– – – of mercury cadmium telluride 954
– – – of II–VI compounds 10
– – – of zinc selenide 1059, 1062, 1068
– – – of zinc sulphide 348, 991
– – – plasma assisted
– – – – of zinc selenide 85
– – through evaporation and condensation
– – – of calcium sulphide 587, 975
– – – of strontium selenide 964
– – – of strontium sulphide 587, 964, 979, 983
– – – of zinc selenide 578
– – – of zinc sulphide 948, 987, 1002, 1030
– – through metalorganic chemical vapor deposition
– – – of cadmium selenide 492, 497, 1077
– – – of cadmium sulphide 492, 497, 532, 536
– – – of cadmium telluride 254, 266, 959, 1073
– – – of cadmium zinc sulphide 119, 501, 536
– – – of mercury cadmium telluride 1, 24, 28, 33, 37, 44, 54, 161, 460
– – – of mercury telluride 49
– – – of zinc cadmium sulphide 353
– – – of zinc chalcogenides 67, 91, 560
– – – of zinc selenide 96, 102, 107, 111, 336, 358, 441, 484, 488, 515, 519, 523, 543, 565, 569, 625, 738, 1075, 1077
– – – of zinc selenide telluride 116
– – – of zinc sulphide 336, 415, 484, 488, 515, 523, 1021, 1035, 1075, 1082
– – – of zinc sulphoselenide 44
– – – of zinc telluride 303, 480, 519, 959
Three–six (III_2–VI_3) compounds 549
Twinning 171, 238
Two–six (II–VI) compounds 10, 67, 156, 420, 492, 549, 592, 634, 640, 682, 715, 738, 742, 907, 1026, 1079, 1083

Uniformity of growth 1082

Vapor growth technique
- by chemical transport
- - of cadmium telluride 259
- - of calcium cadmium sulphide 806
- - of zinc sulphide 721
- by evaporation and condensation
- - of zinc sulphoselenide 328
- theory of 689

Zinc
- cadmium selenide 1040, 1079
- cadmium sulphide 353
- cadmium sulphoselenide 527
- chalcogenides 510, 715
- magnesium sulphoselenide 139
- mercury telluride 197
- oxide 366, 370, 727, 939
- selenide 67, 75, 80, 85, 102, 107, 111, 125, 129, 134, 148, 320, 324, 331, 336, 341, 358, 375, 400, 406, 410, 432, 441, 484, 488, 497, 505, 515, 543, 565, 569, 573, 578, 583, 625, 677, 689, 694, 704, 710, 738, 797, 894, 1055, 1059, 1062, 1068, 1074, 1077, 1078
- selenide telluride 91, 116, 793
- sulphide 152, 336, 420, 484, 488, 497, 505, 515, 583, 689, 718, 721, 935, 943, 948, 987, 991, 997, 1002, 1008, 1012, 1016, 1021, 1026, 1030, 1035
- sulphoselenide 67, 316, 441, 1078
- telluride 144, 297, 396, 470, 480, 505, 519, 913, 1050